LM321LV、LM358LV、LM324LV 行业标准低电压运算放大器

1 特性

- 适用于成本敏感型系统的行业标准放大器
- 低输入失调电压：±1mV
- 共模电压范围包括接地
- 单位增益带宽：1MHz
- 低宽带噪声：40nV/√Hz
- 低静态电流：90µA/通道
- 单位增益稳定
- 可在 2.7V 至 5.5V 的电源电压范围内工作
- 提供单通道、双通道和四通道型号
- 严格的 ESD 规格：2kV HBM
- 工作温度范围：–40°C 至 125°C

2 应用

- 无线电器
- 不间断电源
- 电池组、充电器和测试设备
- 电源模块
- 环境传感器信号调节
- 现场变送器：温度传感器
- 示波器、数字万用表、测试设备
- 机架式服务器
- HVAC：暖通空调
- 直流电机控制
- 低侧电流检测

3 说明

LM3xxLV 系列包括单路 LM321LV、双路 LM358LV 和四路 LM324LV 运算放大器。这些器件由 2.7V 至 5.5V 的低电压供电。

这些运算放大器可在低电压 应用 中替代 LM321、LM358 和 LM324。某些 应用 是大型电器、烟雾探测器和个人电子产品。LM3xxLV 器件在低电压下可提供比 LM3xx 器件更佳的性能，并且功耗更低。这些运算放大器具有单位增益稳定性，并且在过驱情况下不会出现相位反转。ESD 设计为 LM3xxLV 系列提供了至少 2kV 的 HBM 规格。

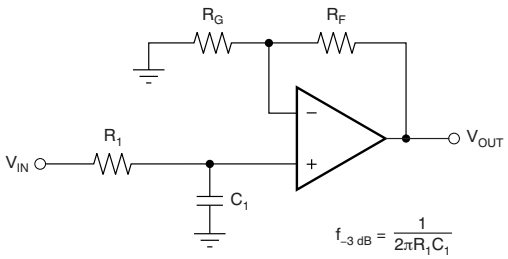
LM3xxLV 系列采用行业标准封装。这些封装包括 SOT-23、SOIC、VSSOP 和 TSSOP 封装。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
LM321LV	SOT-23 (5)	1.60mm × 2.90mm
	SC70 (5)	1.25mm × 2.00mm
LM358LV	SOIC (8)	3.91mm × 4.90mm
	SOT-23 (8)	1.60mm × 2.90mm
	TSSOP (8)	3.00mm × 4.40mm
	VSSOP (8)	3.00mm × 3.00mm
LM324LV	SOIC (14)	8.65mm × 3.91mm
	TSSOP (14)	4.40mm × 5.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

单极低通滤波器



$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right)\left(\frac{1}{1 + sR_1C_1}\right)$$

目录

4 修订历史记录

Changes from Revision C (May 2019) to Revision D — **Page**

- 已删除 删除了数据表中关于 SOT-23 (DDF) 封装的所有预览符号 ... 1

Changes from Revision B (February 2019) to Revision C — **Page**

- 已添加 向*器件信息* 表添加了 SOT-23 (DDF) 封装 ... 1
- Added DDF (SOT-23) information to *Pin Configuration and Functions* section ... 4
- Added DDF (SOT-23) to *Thermal Information: LM358LV* table ... 7

Changes from Revision A (January 2019) to Revision B — **Page**

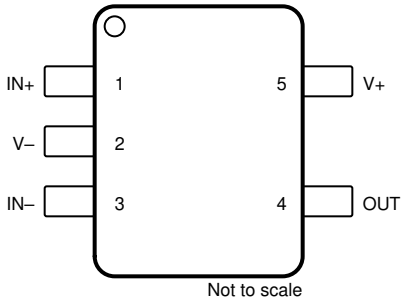
- Changed LM321LVIDBV (SOT-23) pinout diagram to match the LM321LVIDCK (SC70) pinout ... 3

Changes from Original (September 2018) to Revision A — **Page**

- 已更改 数据表标题从“*LM3xxLV...*”更改为“*LM321LV*、*LM358LV*、*LM324LV...*” ... 1

5 Pin Configuration and Functions

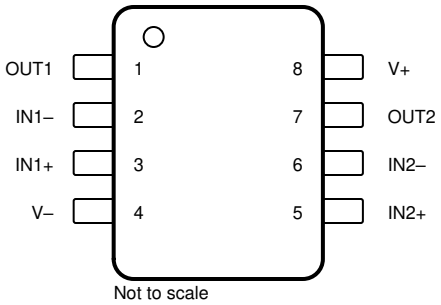
LM321LV DBV, DCK Package
5-Pin SOT-23, SC70
Top View



Pin Functions: LM321LV

PIN		I/O	DESCRIPTION
NAME	NO.		
IN–	3	I	Inverting input
IN+	1	I	Noninverting input
OUT	4	O	Output
V–	2	I or —	Negative (low) supply or ground (for single-supply operation)
V+	5	I	Positive (high) supply

LM358LV D, DGK, PW, DDF Packages
8-Pin SOIC, VSSOP, TSSOP, SOT-23
Top View

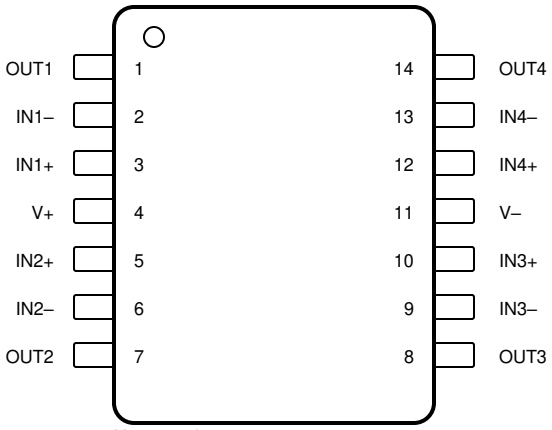


Not to scale

Pin Functions: LM358LV

PIN		I/O	DESCRIPTION
NAME	NO.		
IN1–	2	I	Inverting input, channel 1
IN1+	3	I	Noninverting input, channel 1
IN2–	6	I	Inverting input, channel 2
IN2+	5	I	Noninverting input, channel 2
OUT1	1	O	Output, channel 1
OUT2	7	O	Output, channel 2
V–	4	I or —	Negative (low) supply or ground (for single-supply operation)
V+	8	I	Positive (high) supply

LM324LV D, PW Packages
14-Pin SOIC, TSSOP
Top View



Not to scale

Pin Functions: LM324LV

PIN		I/O	DESCRIPTION
NAME	NO.		
IN1–	2	I	Inverting input, channel 1
IN1+	3	I	Noninverting input, channel 1
IN2–	6	I	Inverting input, channel 2
IN2+	5	I	Noninverting input, channel 2
IN3–	9	I	Inverting input, channel 3
IN3+	10	I	Noninverting input, channel 3
IN4–	13	I	Inverting input, channel 4
IN4+	12	I	Noninverting input, channel 4
OUT1	1	O	Output, channel 1
OUT2	7	O	Output, channel 2
OUT3	8	O	Output, channel 3
OUT4	14	O	Output, channel 4
V–	11	I or —	Negative (low) supply or ground (for single-supply operation)
V+	4	I	Positive (high) supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating junction temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
Supply voltage, ([V+] – [V–])			0	6	V
Signal input pins	Voltage(2)	Common-mode	(V–) – 0.5	(V+) + 0.5	V
		Differential		(V+) – (V–) + 0.2	V
	Current(2)		–10	10	mA
Output short-circuit(3)			Continuous		
Operating, T_A			–55	150	°C
Operating junction temperature, T_J				150	°C
Storage temperature, T_{stg}			–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
(3) Short-circuit to ground, one amplifier per package.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_S	Supply voltage [(V+) – (V–)]	2.7	5.5	V
V_{IN}	Input pin voltage range	(V–) – 0.1	(V+) – 1	V
T_A	Specified temperature	–40	125	°C

6.4 Thermal Information: LM321LV

THERMAL METRIC(1)		LM321LV		UNIT
		DBV (SOT-23)	DCK (SC70)	
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	232.9	239.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	153.8	148.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	100.9	82.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter	77.2	54.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	100.4	81.8	°C/W

(1) For more information about traditional and new thermal metrics, see *Semiconductor and IC Package Thermal Metrics*.

6.5 Thermal Information: LM358LV

THERMAL METRIC(1)		LM358LV				UNIT
		D (SOIC)	DGK (VSSOP)	PW (TSSOP)	DDF (SOT-23)	
		8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	207.9	201.2	200.7	183.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	92.8	85.7	95.4	112.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	129.7	122.9	128.6	98.2	°C/W
ψ_{JT}	Junction-to-top characterization parameter	26	21.2	27.2	18.8	°C/W
ψ_{JB}	Junction-to-board characterization parameter	127.9	121.4	127.2	97.6	°C/W

(1) For more information about traditional and new thermal metrics, see *Semiconductor and IC Package Thermal Metrics*.

6.6 Thermal Information: LM324LV

THERMAL METRIC(1)		LM324LV		UNIT
		D (SOIC)	PW (TSSOP)	
		14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	102.1	148.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	56.8	68.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	58.5	92.7	°C/W
ψ_{JT}	Junction-to-top characterization parameter	20.5	16.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter	58.1	91.8	°C/W

(1) For more information about traditional and new thermal metrics, see *Semiconductor and IC Package Thermal Metrics*.

6.7 Electrical Characteristics

For V_S = (V+) – (V–) = 2.7 V to 5.5 V (±1.35 V to ±2.75 V), T_A = 25°C, R_L = 10 kΩ connected to V_S / 2, and V_{CM} = V_{OUT} = V_S / 2 (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V_{OS}	Input offset voltage	V_S = 5 V		±1	±3	mV
		V_S = 5 V, T_A = –40°C to 125°C			±5	
dV_{OS}/dT	V_{OS} vs temperature	T_A = –40°C to 125°C		±4		µV/°C
PSRR	Power-supply rejection ratio	V_S = 2.7 V to 5.5 V, V_{CM} = (V–)	80	100		dB
INPUT VOLTAGE RANGE						
V_{CM}	Common-mode voltage range	No phase reversal	(V–) – 0.1		(V+) – 1	V
CMRR	Common-mode rejection ratio	V_S = 2.7 V, (V–) – 0.1 V < V_{CM} < (V+) – 1 V, T_A = –40°C to 125°C		84		dB
		V_S = 5.5 V, (V–) – 0.1 V < V_{CM} < (V+) – 1 V, T_A = –40°C to 125°C	63	92		
INPUT BIAS CURRENT						
I_B	Input bias current	V_S = 5 V		±15		pA
I_{OS}	Input offset current			±5		pA
NOISE						
E_n	Input voltage noise (peak-to-peak)	f = 0.1 Hz to 10 Hz, V_S = 5 V		5.1		μV_{PP}
e_n	Input voltage noise density	f = 1 kHz, V_S = 5 V		40		$nV/\sqrt{Hz}$
INPUT CAPACITANCE						
C_{ID}	Differential			2		pF
C_{IC}	Common-mode			5.5		pF
OPEN-LOOP GAIN						
A_{OL}	Open-loop voltage gain	V_S = 2.7 V, (V–) + 0.15 V < V_O < (V+) – 0.15 V, R_L = 2 kΩ		110		dB
		V_S = 5.5 V, (V–) + 0.15 V < V_O < (V+) – 0.15 V, R_L = 2 kΩ		125		
FREQUENCY RESPONSE						
GBW	Gain-bandwidth product	V_S = 5 V		1		MHz
φ_m	Phase margin	V_S = 5.5 V, G = 1		75		°
SR	Slew rate	V_S = 5 V		1.5		V/µs
t_S	Settling time	To 0.1%, V_S = 5 V, 2-V step, G = 1, C_L = 100 pF		4		µs
		To 0.01%, V_S = 5 V, 2-V step, G = 1, C_L = 100 pF		5		
t_{OR}	Overload recovery time	V_S = 5 V, V_{IN} × gain > V_S		1		µs
THD+N	Total harmonic distortion + noise	V_S = 5.5 V, V_{CM} = 2.5 V, V_O = 1 V_{RMS}, G = 1, f = 1 kHz, 80-kHz measurement BW		0.005%		
OUTPUT						
V_{OH}	Voltage output swing from positive supply	R_L ≥ 2 kΩ, T_A = –40°C to 125°C	1			V
V_{OL}	Voltage output swing from negative supply	R_L ≤ 10 kΩ, T_A = –40°C to 125°C		40	75	mV
I_{SC}	Short-circuit current	V_S = 5.5 V		±40		mA
Z_O	Open-loop output impedance	V_S = 5 V, f = 1 MHz		1200		Ω
POWER SUPPLY						
V_S	Specified voltage range		2.7 (±1.35)		5.5 (±2.75)	V
I_Q	Quiescent current per amplifier	I_O = 0 mA, V_S = 5.5 V		90	150	µA
		I_O = 0 mA, V_S = 5.5 V, T_A = –40°C to 125°C			160	

6.8 Typical Characteristics

at T_A = 25°C, V+ = 2.75 V, V– = –2.75 V, R_L = 10 kΩ connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted)

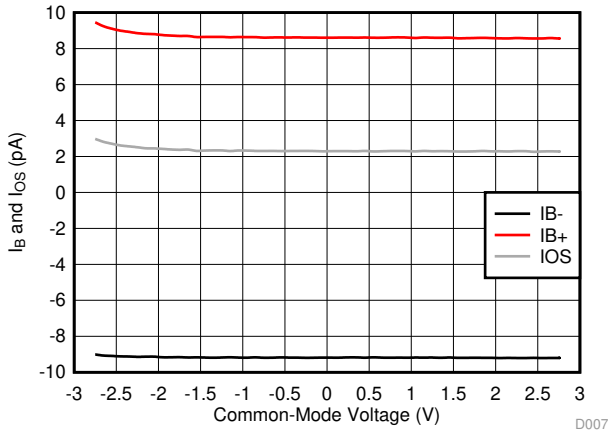


图 1. I_B and I_{OS} vs Common-Mode Voltage

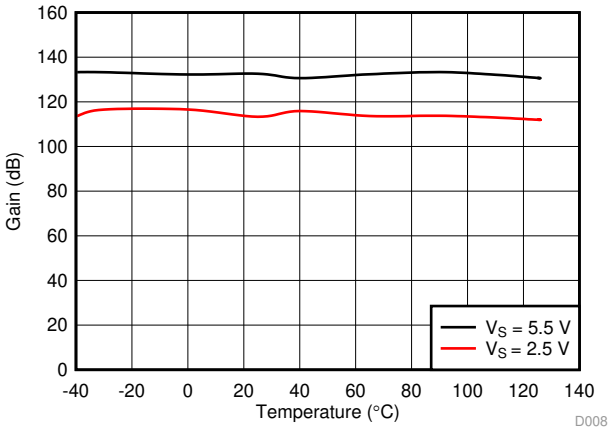
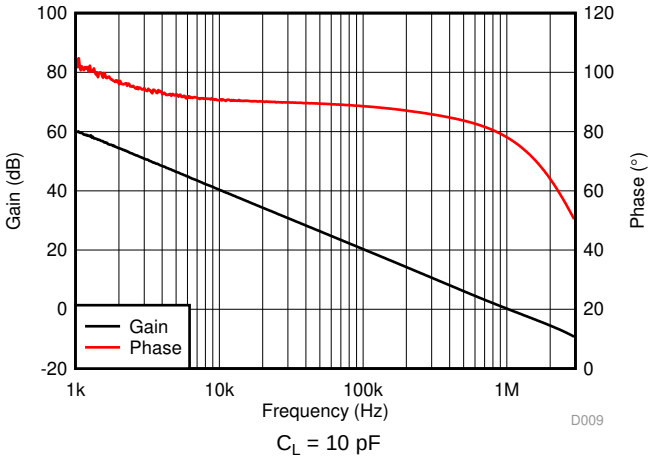


图 2. Open-Loop Gain vs Temperature



C_L = 10 pF

图 3. Open-Loop Gain and Phase vs Frequency

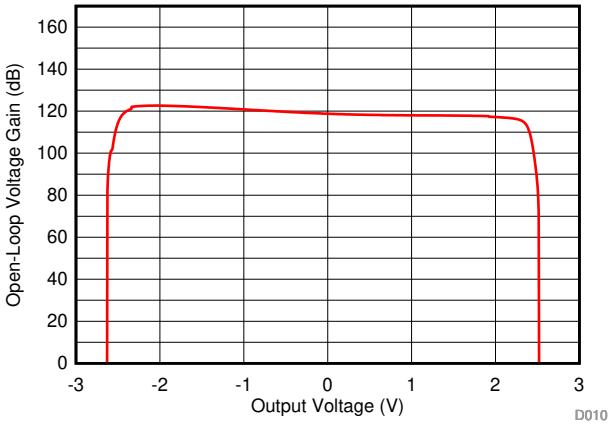
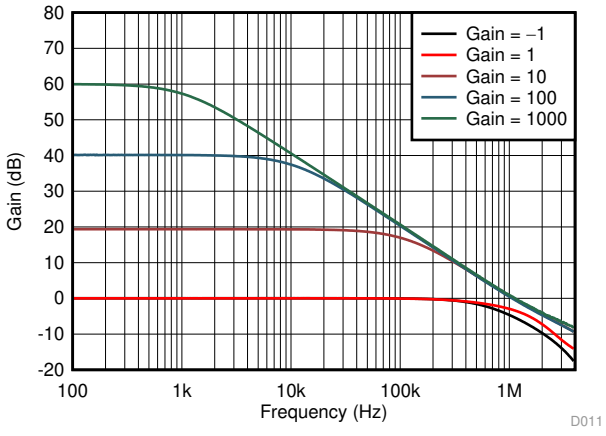


图 4. Open-Loop Voltage Gain vs Output Voltage



C_L = 10 pF

图 5. Closed-Loop Gain vs Frequency

Typical Characteristics (接下页)

at T_A = 25°C, V+ = 2.75 V, V– = –2.75 V, R_L = 10 kΩ connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted)

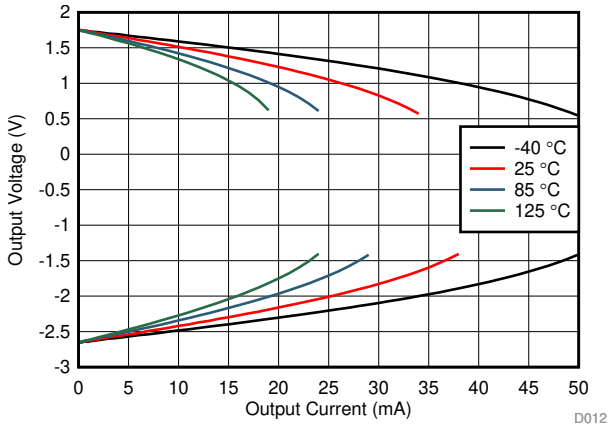


图 6. Output Voltage vs Output Current (Claw)

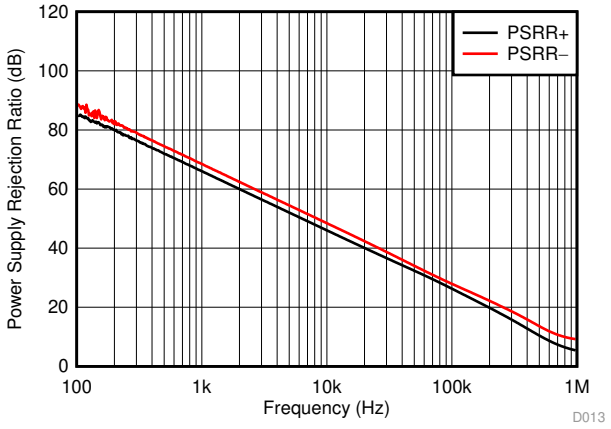
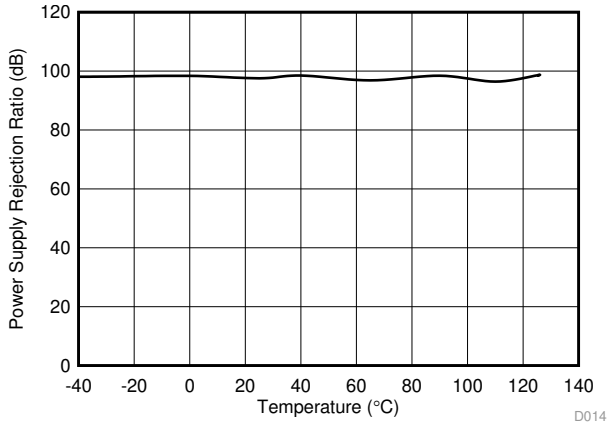


图 7. PSRR vs Frequency



V_S = 2.7 V to 5.5 V

图 8. DC PSRR vs Temperature

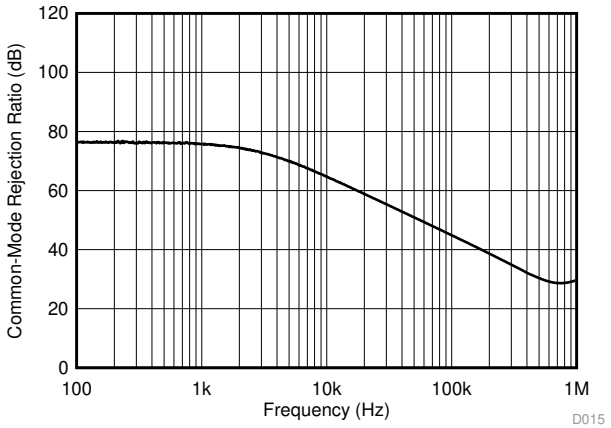
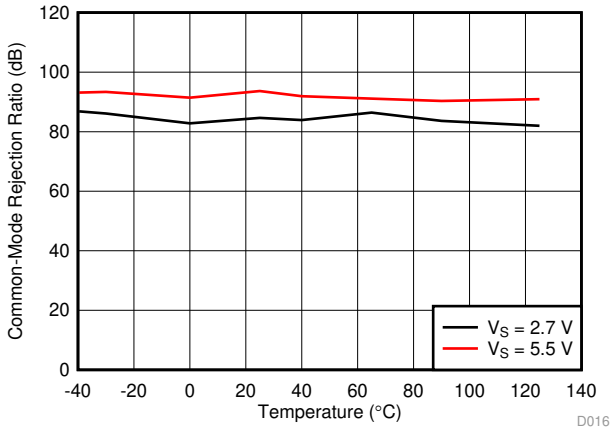


图 9. CMRR vs Frequency



V_{CM} = (V–) – 0.1 V to (V+) – 1.5 V

图 10. DC CMRR vs Temperature

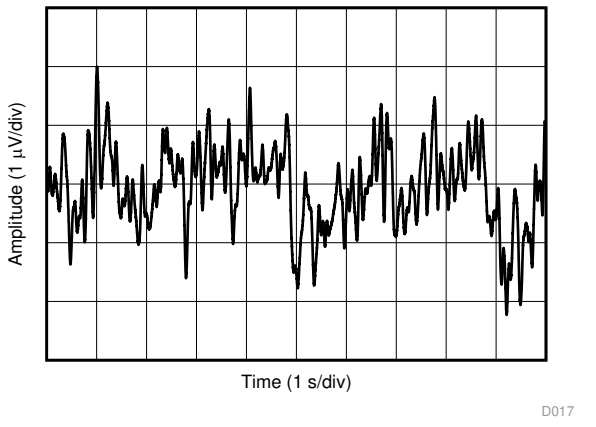


图 11. 0.1-Hz to 10-Hz Integrated Voltage Noise

Typical Characteristics (接下页)

at T_A = 25°C, V+ = 2.75 V, V– = –2.75 V, R_L = 10 kΩ connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted)

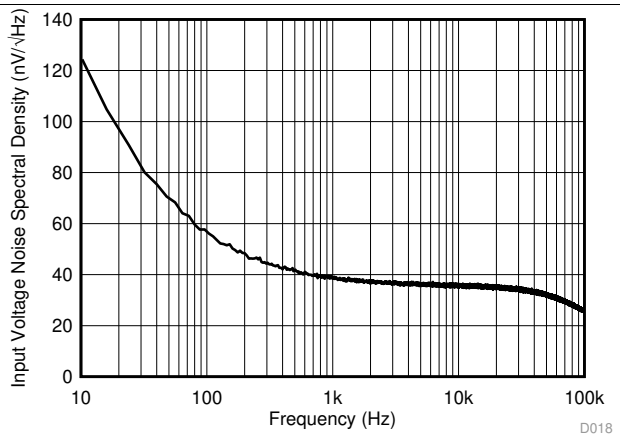
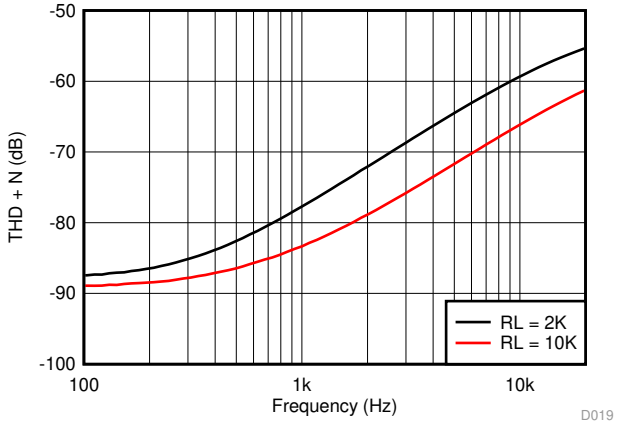
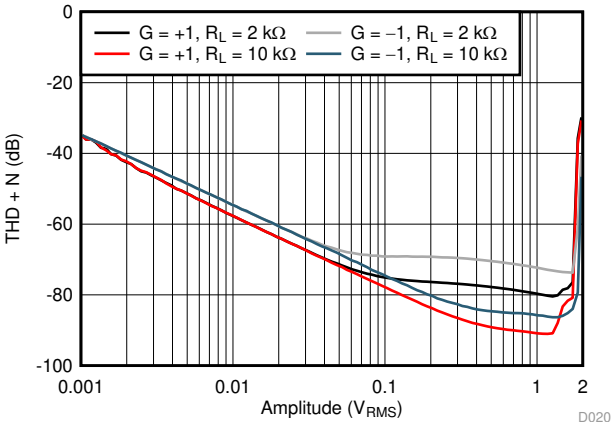


图 12. Input Voltage Noise Spectral Density



V_S = 5.5 V
BW = 80 kHz
V_{CM} = 2.5 V
V_{OUT} = 0.5 V_{RMS}
G = 1

图 13. THD + N vs Frequency



V_S = 5.5 V
BW = 80 kHz
V_{CM} = 2.5 V
f = 1 kHz
G = 1

图 14. THD + N vs Amplitude

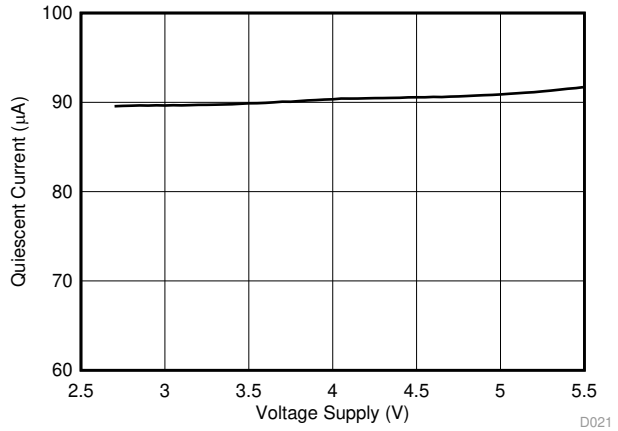


图 15. Quiescent Current vs Supply Voltage

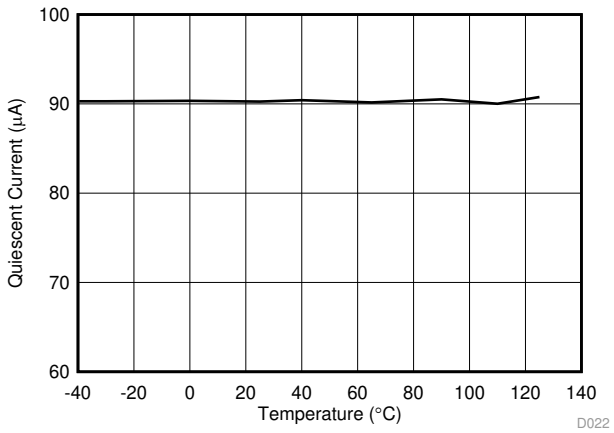


图 16. Quiescent Current vs Temperature

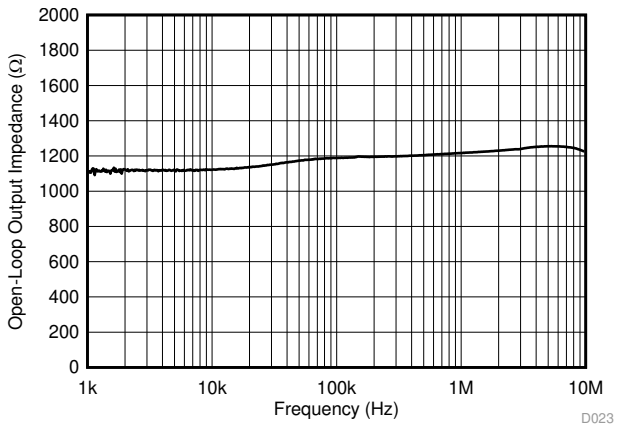
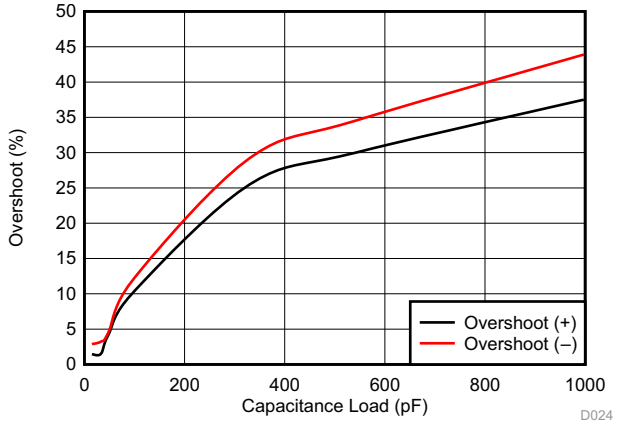


图 17. Open-Loop Output Impedance vs Frequency

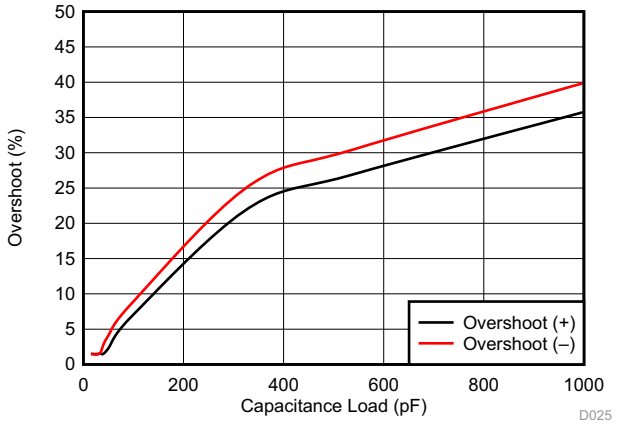
Typical Characteristics (接下页)

at T_A = 25°C, V+ = 2.75 V, V– = –2.75 V, R_L = 10 kΩ connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted)



G = 1 V_{IN} = 100 mVpp

图 18. Small Signal Overshoot vs Capacitive Load



G = –1 V_{IN} = 100 mVpp

图 19. Small Signal Overshoot vs Capacitive Load

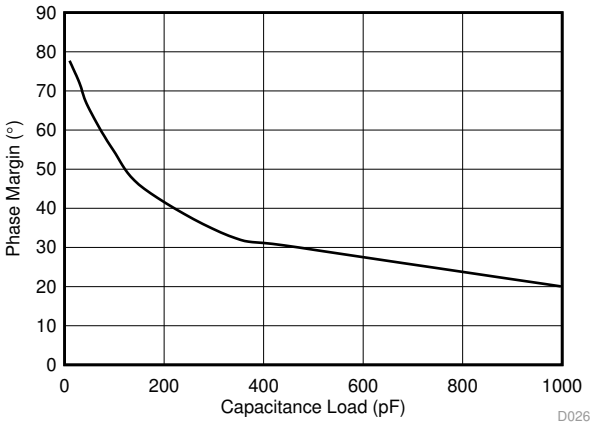
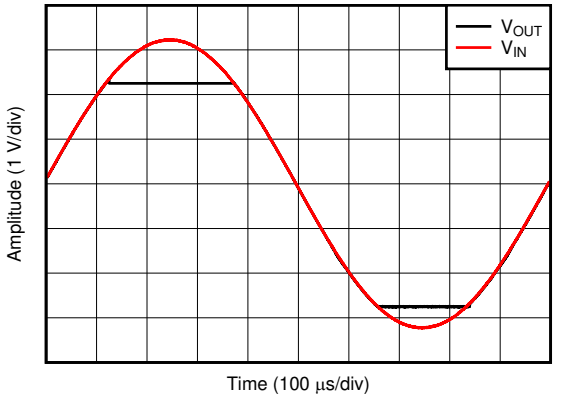
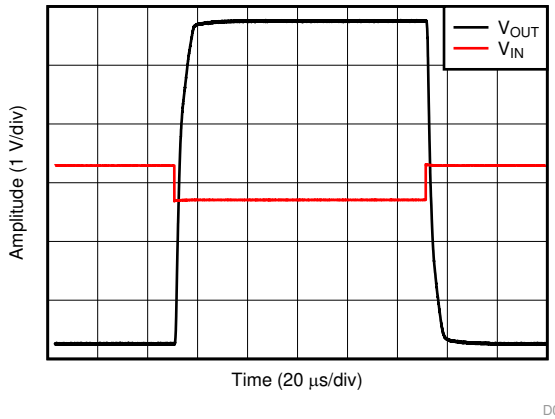


图 20. Phase Margin vs Capacitive Load



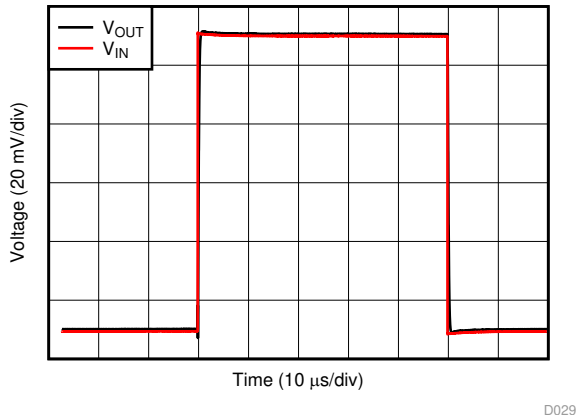
G = 1 V_{IN} = 6.5 V_{PP}

图 21. No Phase Reversal



G = –10 V_{IN} = 600 mV_{PP}

图 22. Overload Recovery

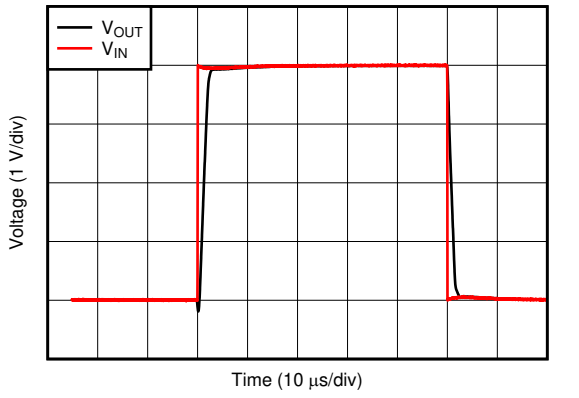


G = 1 V_{IN} = 100 mV_{PP} C_L = 10 pF

图 23. Small-Signal Step Response

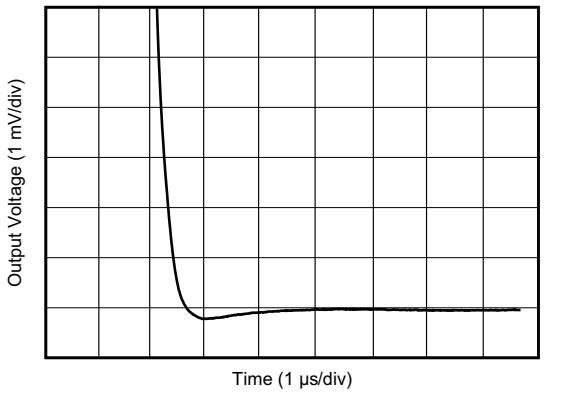
Typical Characteristics (接下页)

at T_A = 25°C, V+ = 2.75 V, V– = –2.75 V, R_L = 10 kΩ connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted)



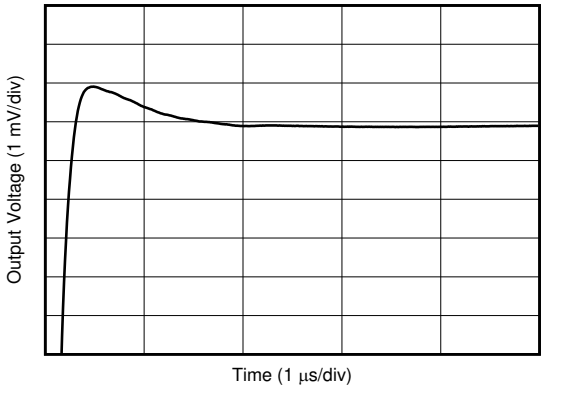
G = 1 V_{IN} = 4 V_{PP} C_L = 10 pF

图 24. Large-Signal Step Response



G = 1 C_L = 100 pF 2-V step

图 25. Large-Signal Settling Time (Negative)



G = 1 C_L = 100 pF 2-V step

图 26. Large-Signal Settling Time (Positive)

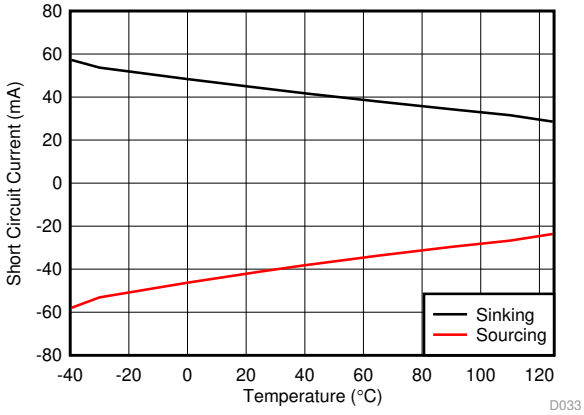


图 27. Short-Circuit Current vs Temperature

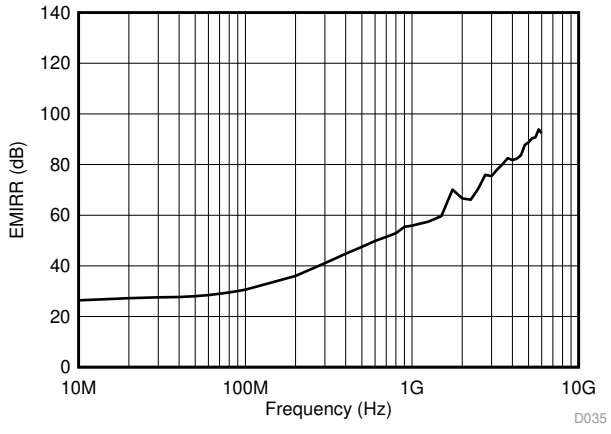


图 28. Electromagnetic Interference Rejection Ratio Referred to Noninverting Input (EMIRR+) vs Frequency

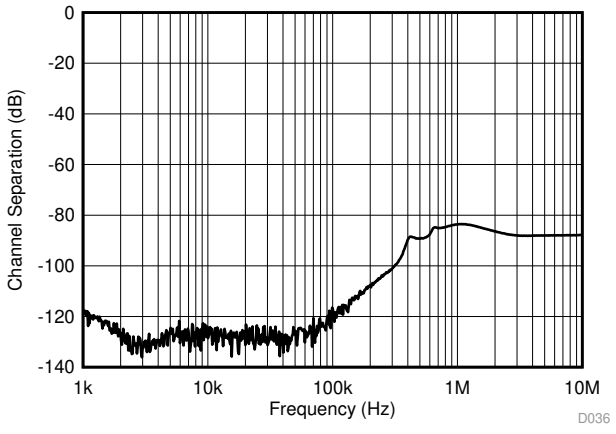


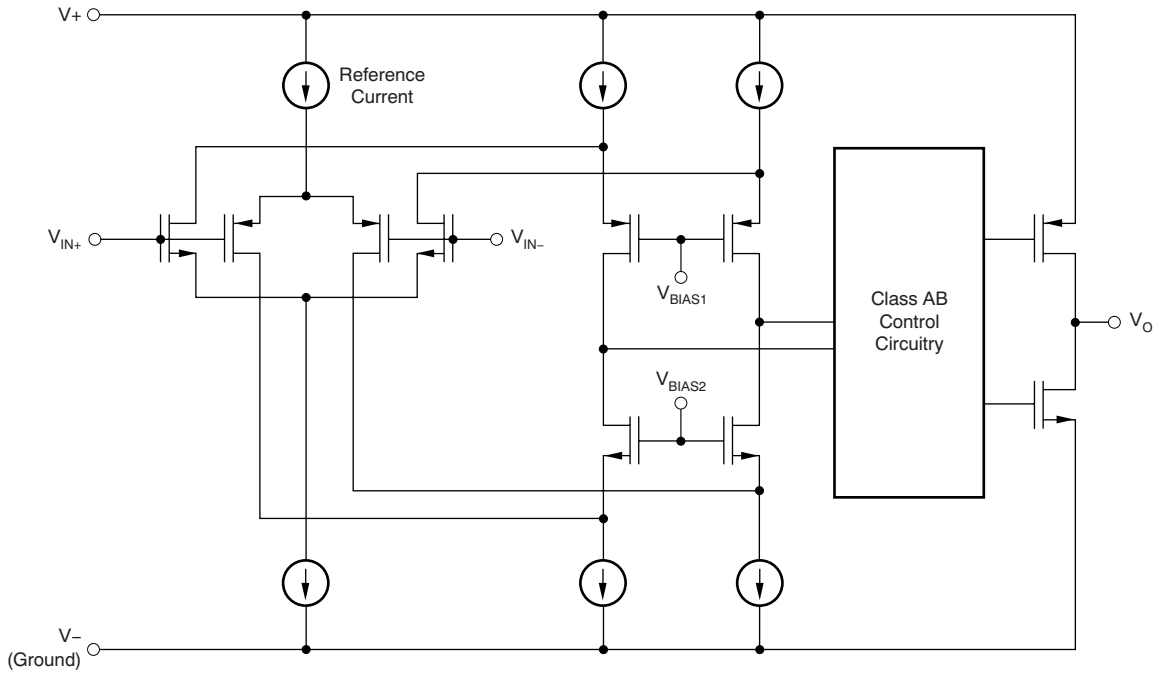
图 29. Channel Separation

7 Detailed Description

7.1 Overview

The LM3xxLV family of low-power op amps is intended for cost-optimized systems. These devices operate from 2.7 V to 5.5 V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The input common-mode voltage range includes the negative rail and allows the LM3xxLV family to be used in many single-supply applications.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Operating Voltage

The LM3xxLV family of op amps is specified for operation from 2.7 V to 5.5 V. In addition, many specifications apply from –40°C to 125°C. Parameters that vary significantly with operating voltages or temperature are shown in the *Electrical Characteristics* section.

7.3.2 Common-Mode Input Range Includes Ground

The input common-mode voltage range of the LM3xxLV family extends to the negative supply rail and within 1 V below the positive rail for the full supply voltage range of 2.7 V to 5.5 V. This performance is achieved with a P-channel differential pair, as shown in the *Functional Block Diagram*. Additionally, a complementary N-channel differential pair has been included in parallel to eliminate issues with phase reversal that are common with previous generations of op amps. However, the N-channel pair is not optimized for operation, and significant performance degradation occurs while this pair is operational. TI recommends limiting any voltage applied at the inputs to at least 1 V below the positive supply rail (V+) to ensure that the op amp conforms to the specifications detailed in the *Electrical Characteristics* section.

Feature Description (接下页)

7.3.3 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the specified output voltage swing, because of the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return to the linear state. After the charge carriers return to the linear state, the device begins to slew at the specified slew rate. Therefore, the propagation delay (in case of an overload condition) is the sum of the overload recovery time and the slew time. The overload recovery time for the LM3xxLV family is typically 1 µs.

7.3.4 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but can also involve the supply voltage pins. Each of these different pin functions has electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

Having a good understanding of this basic ESD circuitry and its relevance to an electrical overstress event is helpful. 图 30 shows the ESD circuits contained in the LM3xxLV. The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power supply lines, where they meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

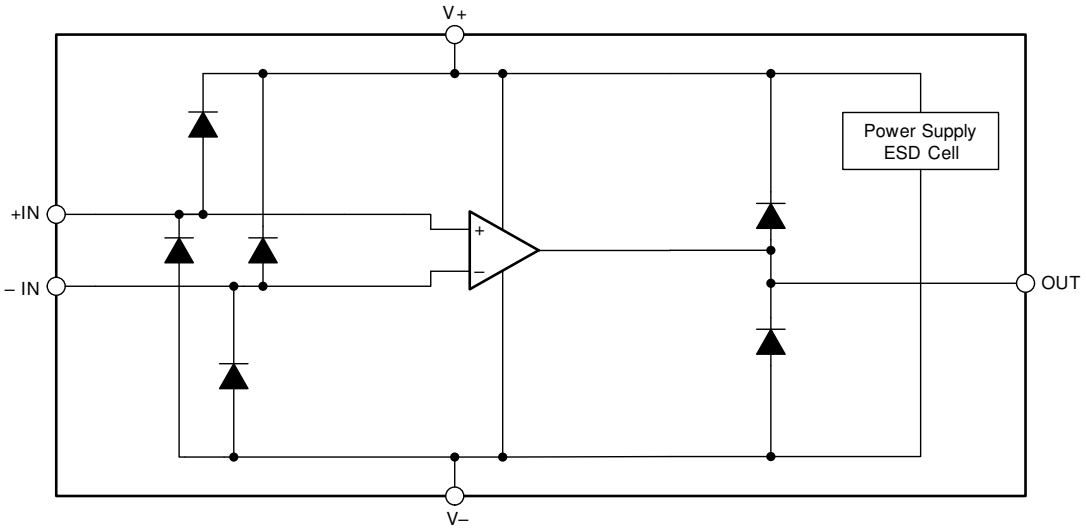


图 30. Equivalent Internal ESD Circuitry

7.3.5 EMI Susceptibility and Input Filtering

Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10 MHz to 6 GHz. The 图 28 plot illustrates the performance of the LM3xxLV family's EMI filters across a wide range of frequencies. For more detailed information, see *EMI Rejection Ratio of Operational Amplifiers* available for download from www.ti.com.

7.4 Device Functional Modes

The LM3xxLV family has a single functional mode. The devices are powered on as long as the power-supply voltage is between 2.7 V (±1.35 V) and 5.5 V (±2.75 V).

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The LM3xxLV devices are a family of low-power, cost-optimized operational amplifiers. The devices operate from 2.7 V to 5.5 V, are unity-gain stable, and are suitable for a wide range of general-purpose applications. The input common-mode voltage range includes the negative rail, and allows the LM3xxLV to be used in any single-supply applications.

8.2 Typical Application

图 31 shows the LM3xxLV device configured in a low-side current sensing application.

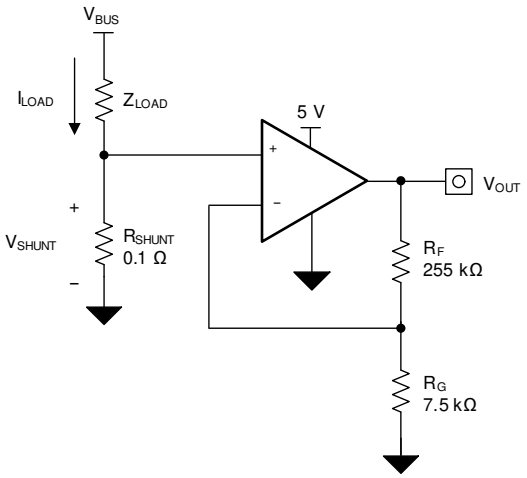


图 31. LM3xxLV Device in a Low-Side, Current-Sensing Application

8.2.1 Design Requirements

The design requirements for this design are:

- Load current: 0 A to 1 A
- Output voltage: 3.5 V
- Maximum shunt voltage: 100 mV

8.2.2 Detailed Design Procedure

The transfer function of the circuit in 图 31 is given in 公式 1:

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times Gain \quad (1)$$

The load current (I_{LOAD}) produces a voltage drop across the shunt resistor (R_{SHUNT}). The load current is set from 0 A to 1 A. To keep the shunt voltage below 100 mV at maximum load current, the largest allowable shunt resistor is shown using 公式 2:

$$R_{SHUNT} = \frac{V_{SHUNT\_MAX}}{I_{LOAD\_MAX}} = \frac{100mV}{1A} = 100m\Omega \quad (2)$$

Typical Application (接下页)

Using 公式 2, R_{SHUNT} is calculated to be 100 mΩ. The voltage drop produced by I_{LOAD} and R_{SHUNT} is amplified by the LM3xxLV device to produce an output voltage of approximately 0 V to 3.5 V. The gain needed by the LM3xxLV to produce the necessary output voltage is calculated using 公式 3:

$$\text{Gain} = \frac{\left(V_{OUT\_MAX} - V_{OUT\_MIN}\right)}{\left(V_{IN\_MAX} - V_{IN\_MIN}\right)} \tag{3}$$

Using 公式 3, the required gain is calculated to be 35 V/V, which is set with resistors R_F and R_G. 公式 4 sizes the resistors R_F and R_G, to set the gain of the LM3xxLV device to 35 V/V.

$$\text{Gain} = 1 + \frac{\left(R_F\right)}{\left(R_G\right)} \tag{4}$$

8.2.3 Application Curve

Selecting R_F as 255 kΩ and R_G as 7.5 kΩ provides a combination that equals 35 V/V. 图 32 shows the measured transfer function of the circuit shown in 图 31. Notice that the gain is only a function of the feedback and gain resistors. This gain is adjusted by varying the ratio of the resistors and the actual resistors values are determined by the impedance levels that the designer wants to establish. The impedance level determines the current drain, the effect that stray capacitance has, and a few other behaviors. There is no optimal impedance selection that works for every system, you must choose an impedance that is ideal for your system parameters.

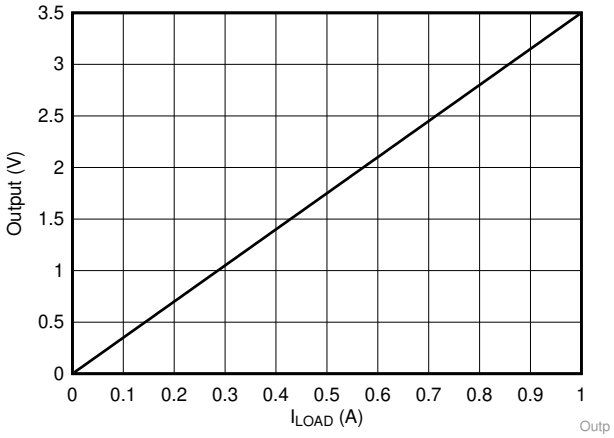


图 32. Low-Side, Current-Sense Transfer Function

9 Power Supply Recommendations

The LM3xxLV family is specified for operation from 2.7 V to 5.5 V (±1.35 V to ±2.75 V); many specifications apply from –40°C to 125°C. The *Electrical Characteristics* section presents parameters that may exhibit significant variance with regard to operating voltage or temperature.

CAUTION

Supply voltages larger than 6 V may permanently damage the device; see the *Absolute Maximum Ratings* table.

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce coupling errors from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the *Layout Guidelines* section.

9.1 Input and ESD Protection

The LM3xxLV family incorporates internal ESD protection circuits on all pins. For input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA, as stated in the *Absolute Maximum Ratings* table. 图 33 shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

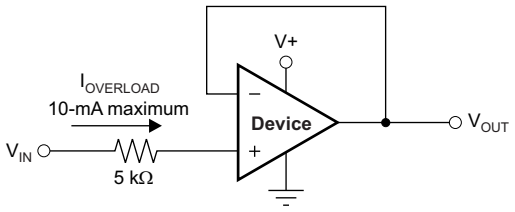


图 33. Input Current Protection

10 Layout

10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and of the op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Take care to physically separate digital and analog grounds. Use thermal signatures or EMI measurement techniques to determine where the majority of the ground current is flowing and be sure to route this path away from sensitive analog circuitry. For more detailed information, see *Circuit Board Layout Techniques*.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace at a 90 degree angle is much better as opposed to running the traces in parallel with the noisy trace.
- Place the external components as close to the device as possible, as shown in 图 35. Keeping R_F and R_G close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring may significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts resulting from moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

10.2 Layout Example

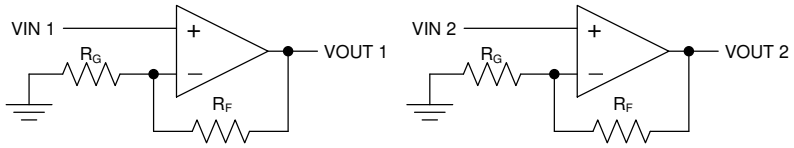


图 34. Schematic Representation for 图 35

Layout Example (接下页)

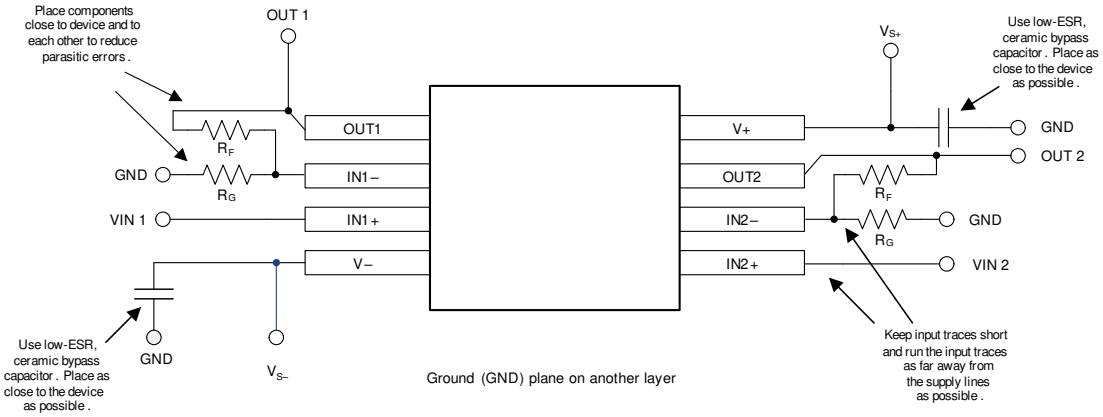


图 35. Layout Example

11 器件和文档支持

11.1 文档支持

11.1.1 相关文档

请参阅如下相关文档：

- 德州仪器 (TI)，*《运算放大器的 EMI 抑制比》*

11.2 相关链接

下表列出了快速访问链接。类别包括技术文档、支持和社区资源、工具和软件，以及立即订购快速访问。

表 1. 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持和社区
LM321LV	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
LM324LV	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
LM358LV	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

11.3 接收文档更新通知

要接收文档更新通知，请导航至 ti.com. 上的器件产品文件夹。单击右上角的*通知我*进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.4 社区资源

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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11.5 商标

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11.6 静电放电警告

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查看左侧的导航面板。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LM321LVIDBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1SPF	Samples
LM321LVIDCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	SN	Level-2-260C-1 YEAR	-40 to 125	1DH	Samples
LM324LVIDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LM324LV	Samples
LM324LVIPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	SN	Level-2-260C-1 YEAR	-40 to 125	LM324LV	Samples
LM358LVIDDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L58L	Samples
LM358LVIDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1PKX	Samples
LM358LVIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	SN	Level-2-260C-1 YEAR	-40 to 125	L358LV	Samples
LM358LVIPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	SN	Level-2-260C-1 YEAR	-40 to 125	358LV	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

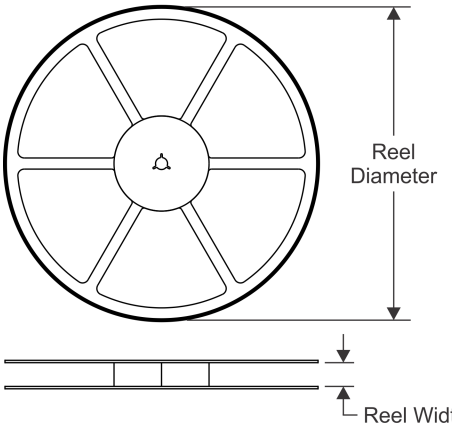
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

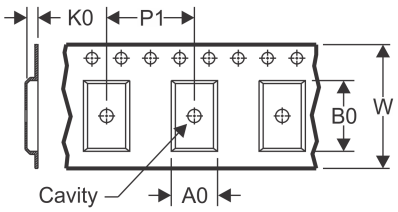
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

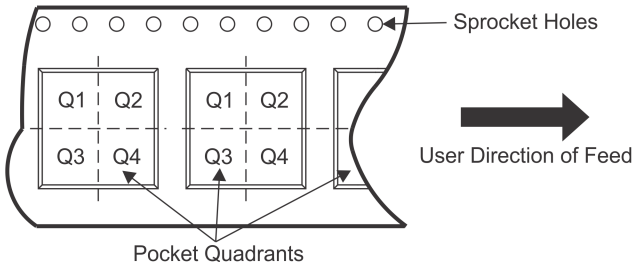


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

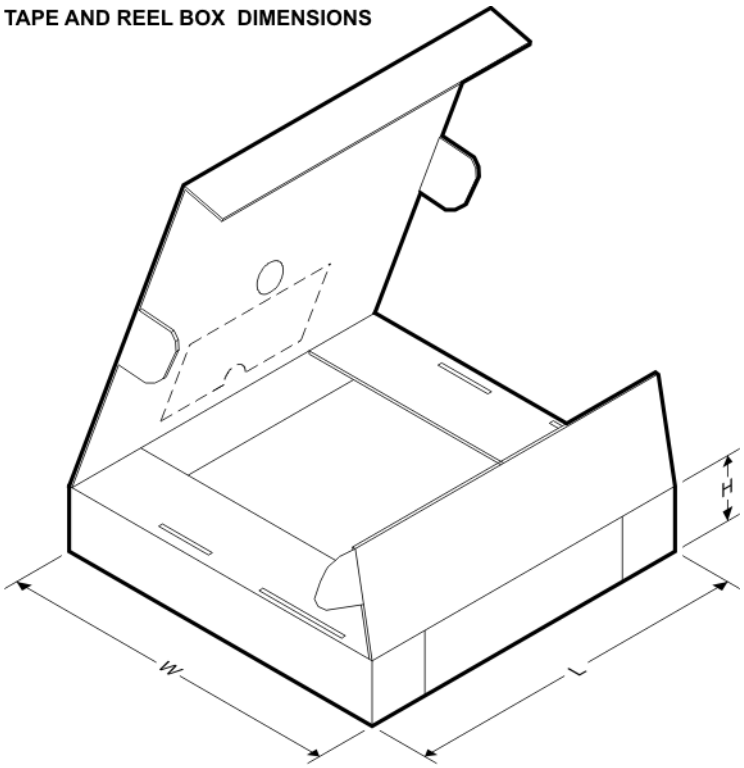
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM321LVIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM321LVIDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
LM324LVIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
LM324LVIDR	SOIC	D	14	2500	330.0	15.4	6.4	5.2	2.1	8.0	12.0	Q1
LM324LVIPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
LM358LVIDDFR	SOT-23-THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM358LVIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM358LVIDR	SOIC	D	8	2500	330.0	15.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358LVIPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

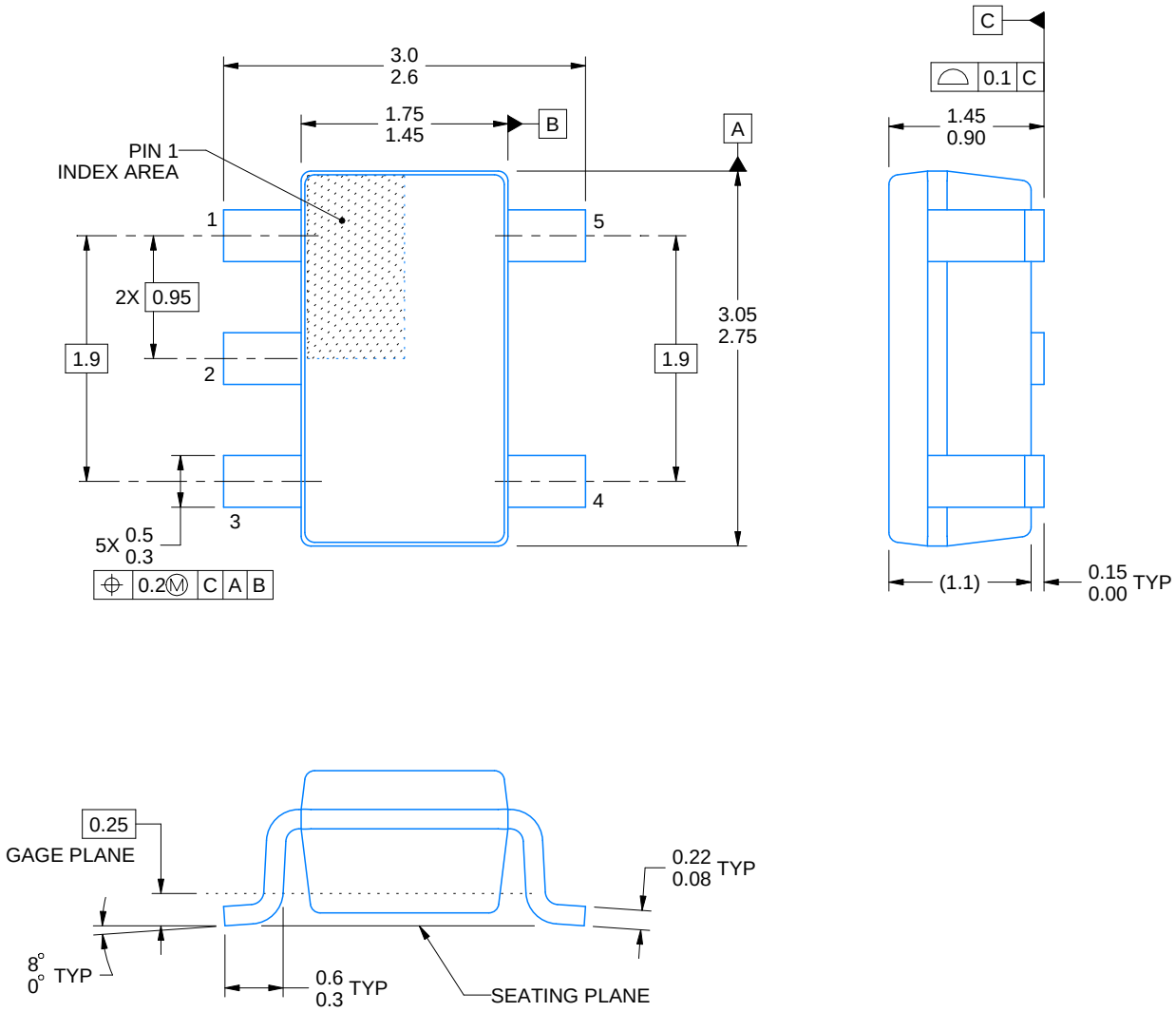
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM321LVIDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
LM321LVIDCKR	SC70	DCK	5	3000	190.0	190.0	30.0
LM324LVIDR	SOIC	D	14	2500	367.0	367.0	38.0
LM324LVIDR	SOIC	D	14	2500	336.6	336.6	41.3
LM324LVIPWR	TSSOP	PW	14	2000	366.0	364.0	50.0
LM358LVIDDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
LM358LVIDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
LM358LVIDR	SOIC	D	8	2500	336.6	336.6	41.3
LM358LVIPWR	TSSOP	PW	8	2000	366.0	364.0	50.0

PACKAGE OUTLINE

DBV0005A

SOT-23 - 1.45 mm max height

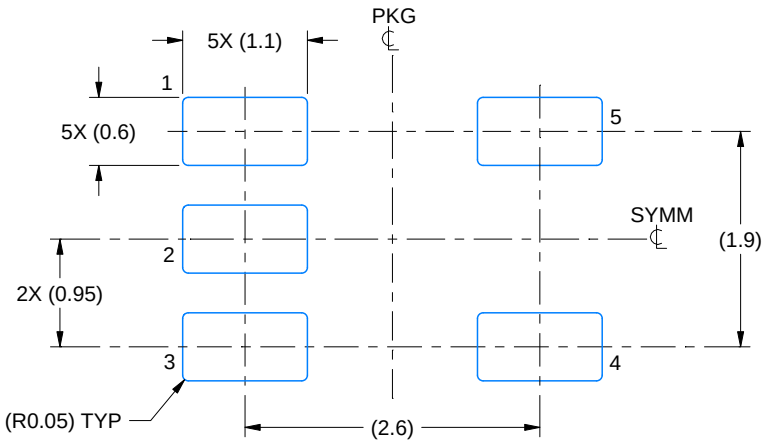
SMALL OUTLINE TRANSISTOR



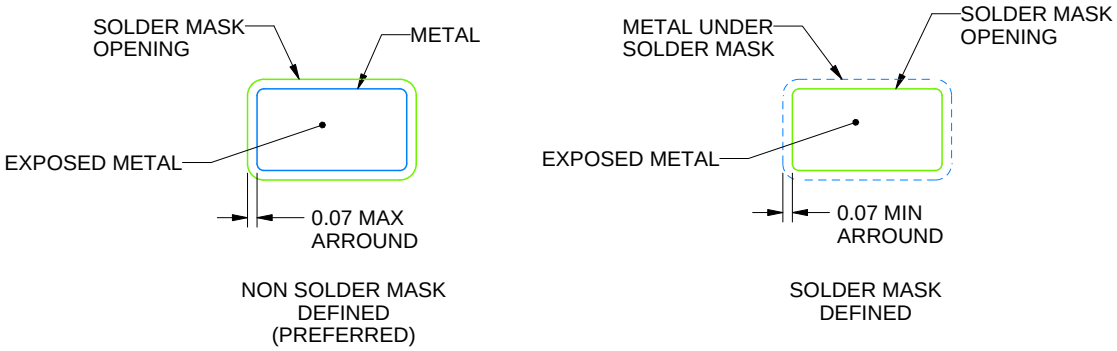
4214839/E 09/2019

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

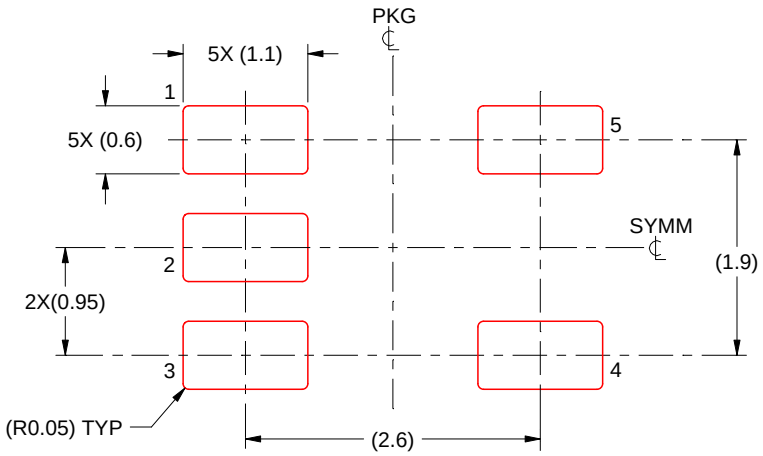


SOLDER MASK DETAILS

4214839/E 09/2019

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



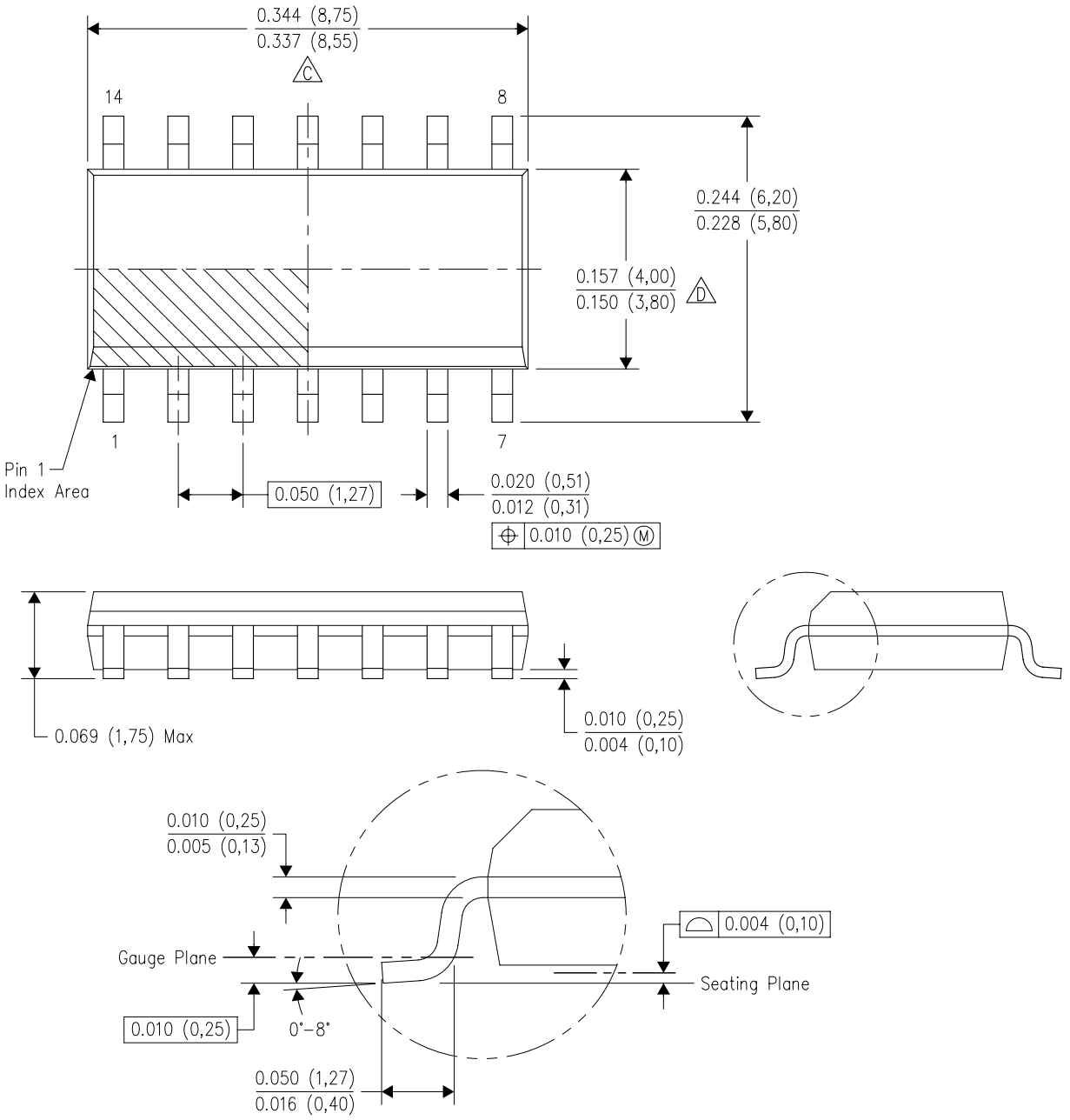
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/E 09/2019

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

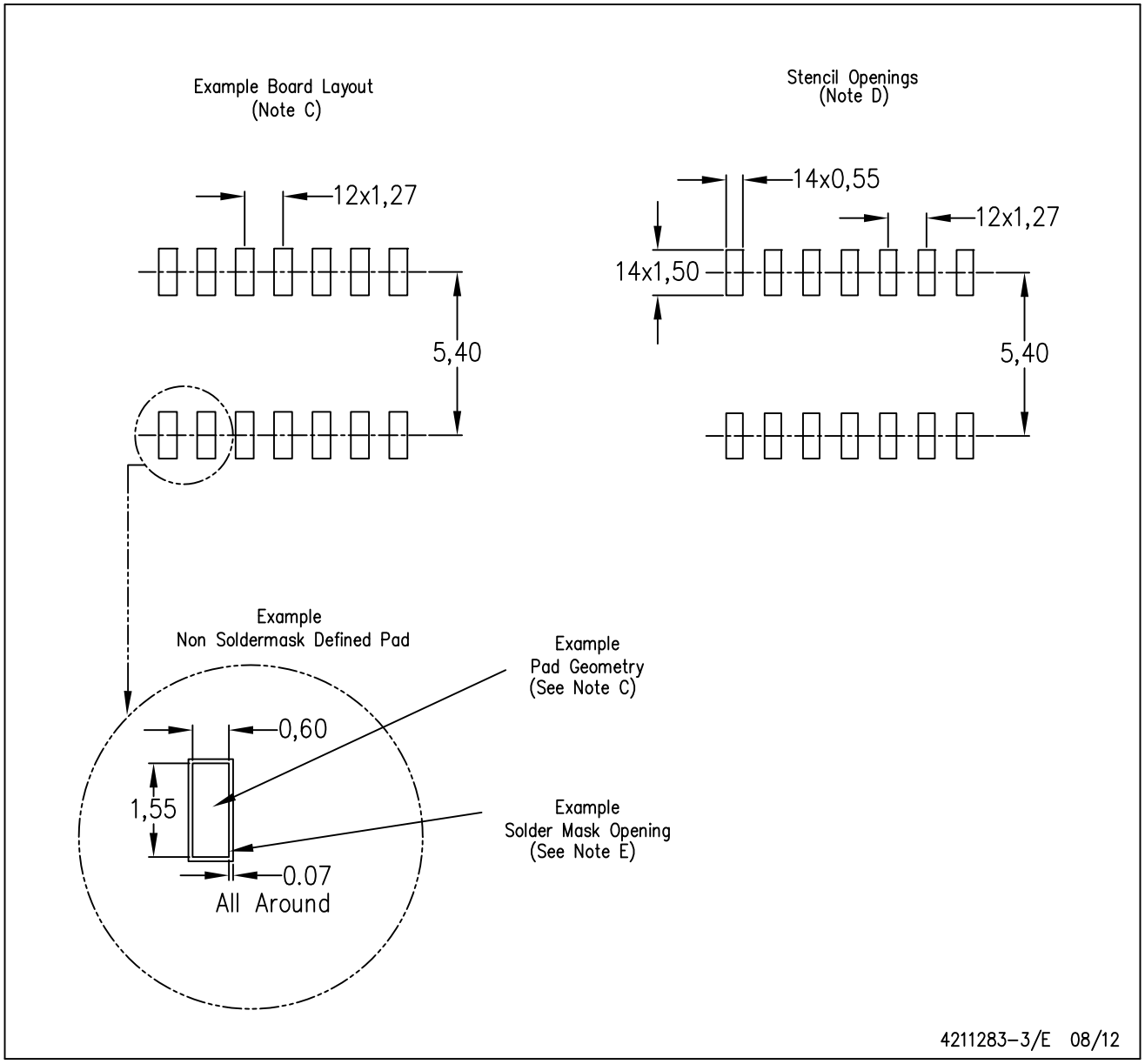
D (R–PDSO–G14) PLASTIC SMALL OUTLINE



4040047–5/M 06/11

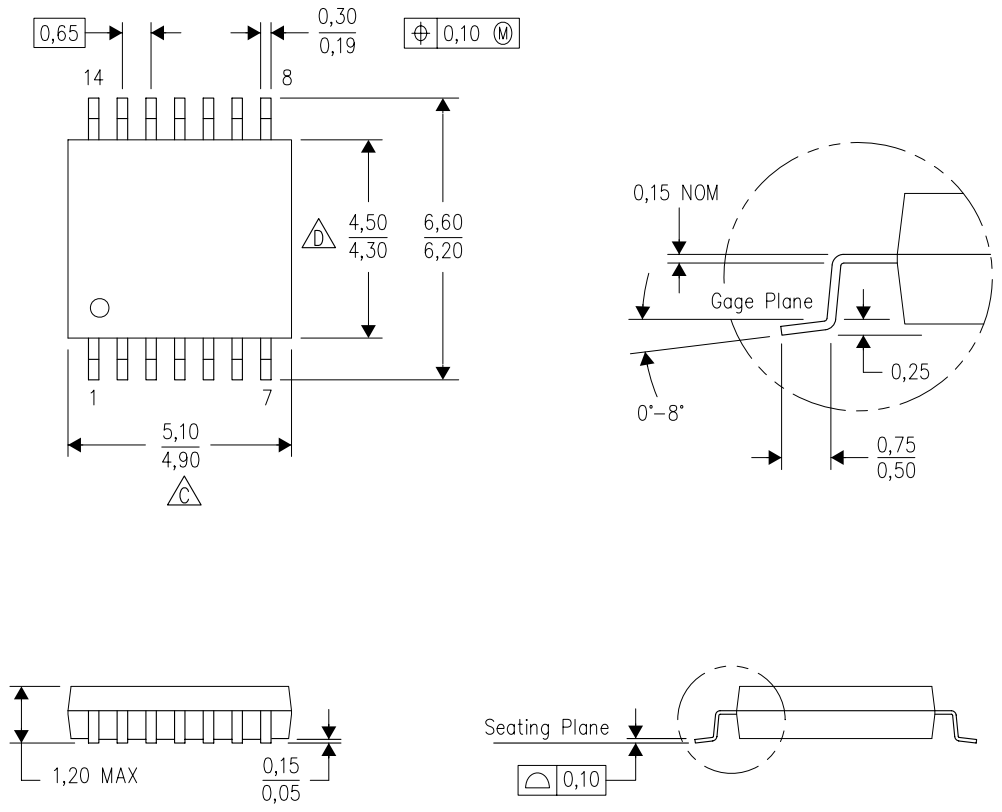
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AB.

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

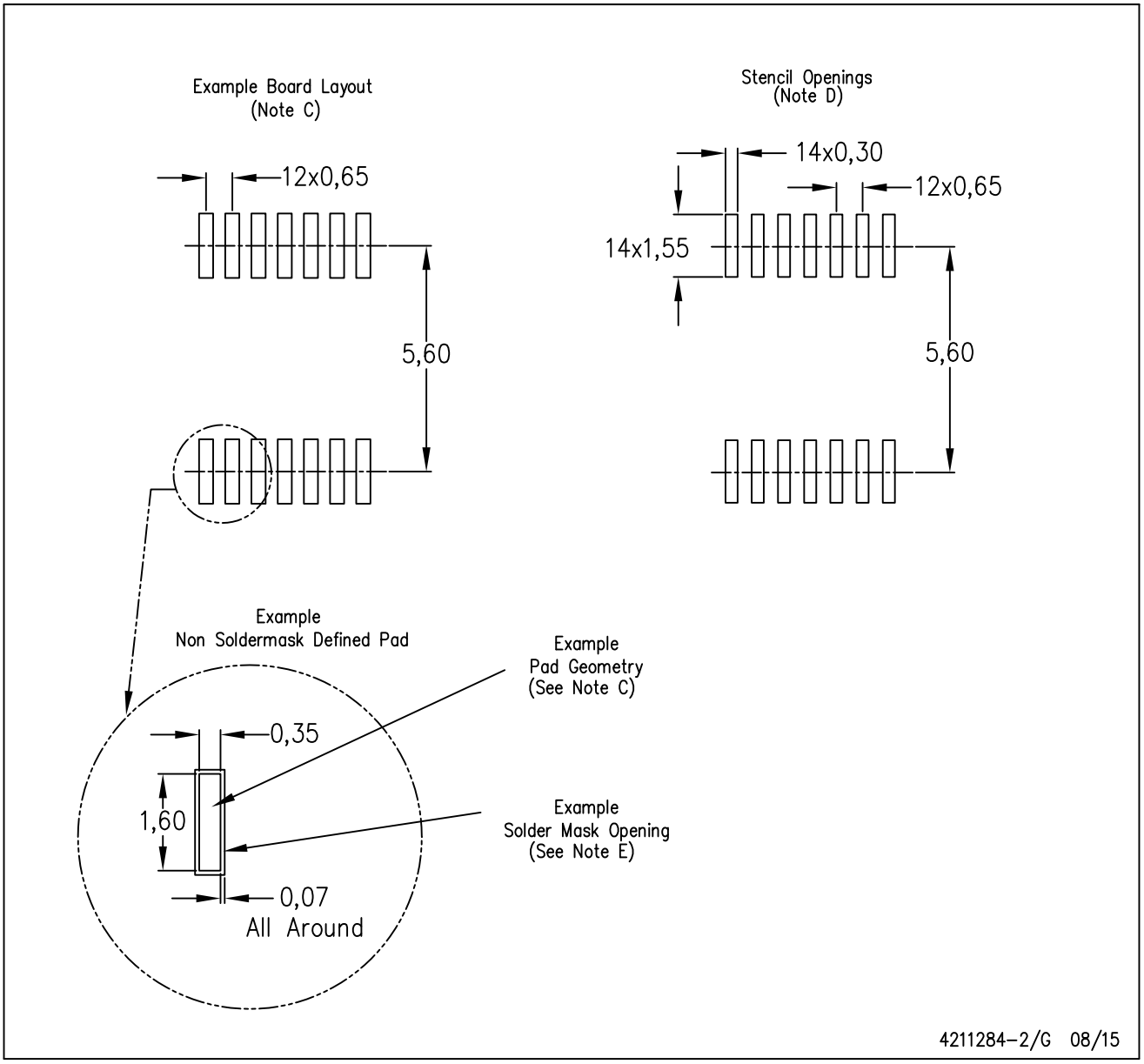
PW (R–PDSO–G14) PLASTIC SMALL OUTLINE



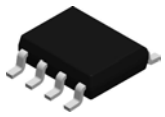
4040064–3/G 02/11

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

PW (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

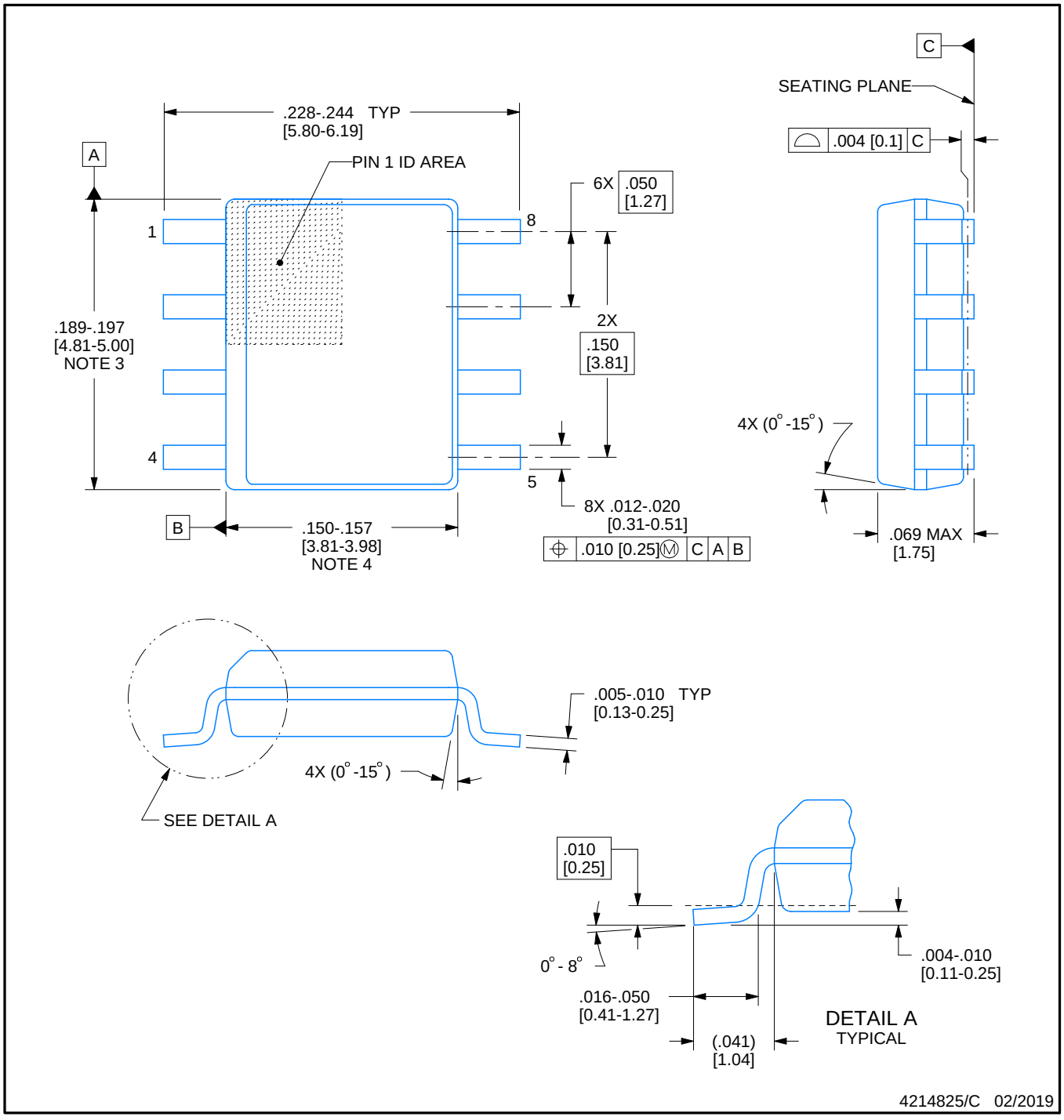


PACKAGE OUTLINE

D0008A

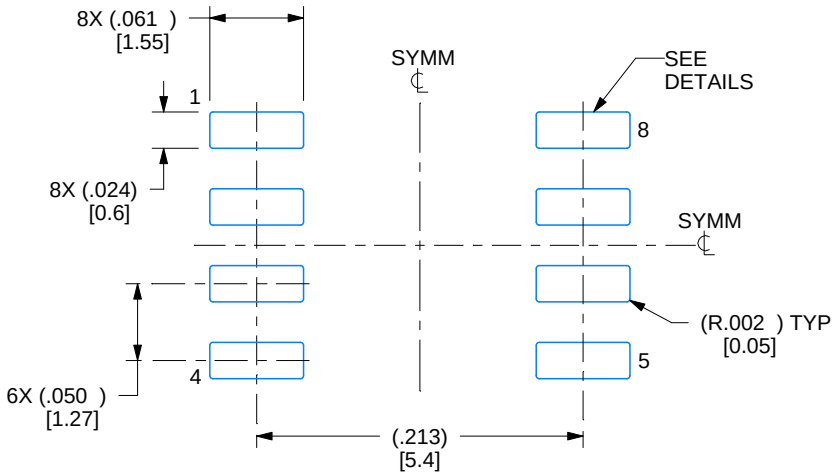
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

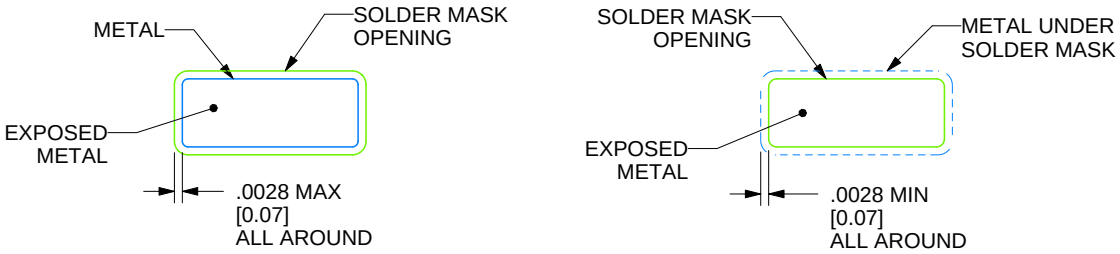


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

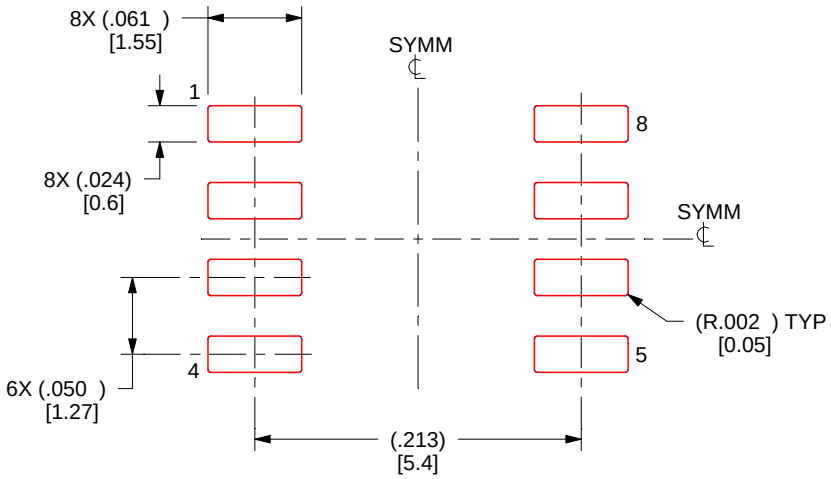
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



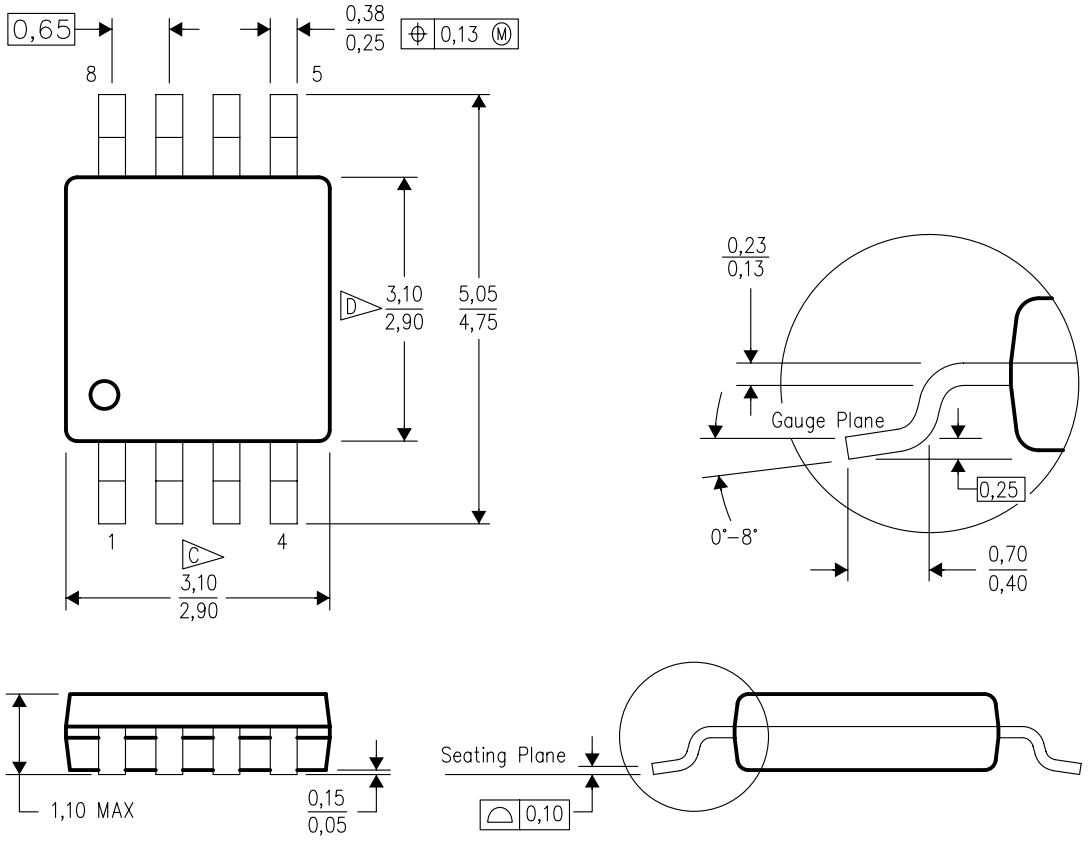
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

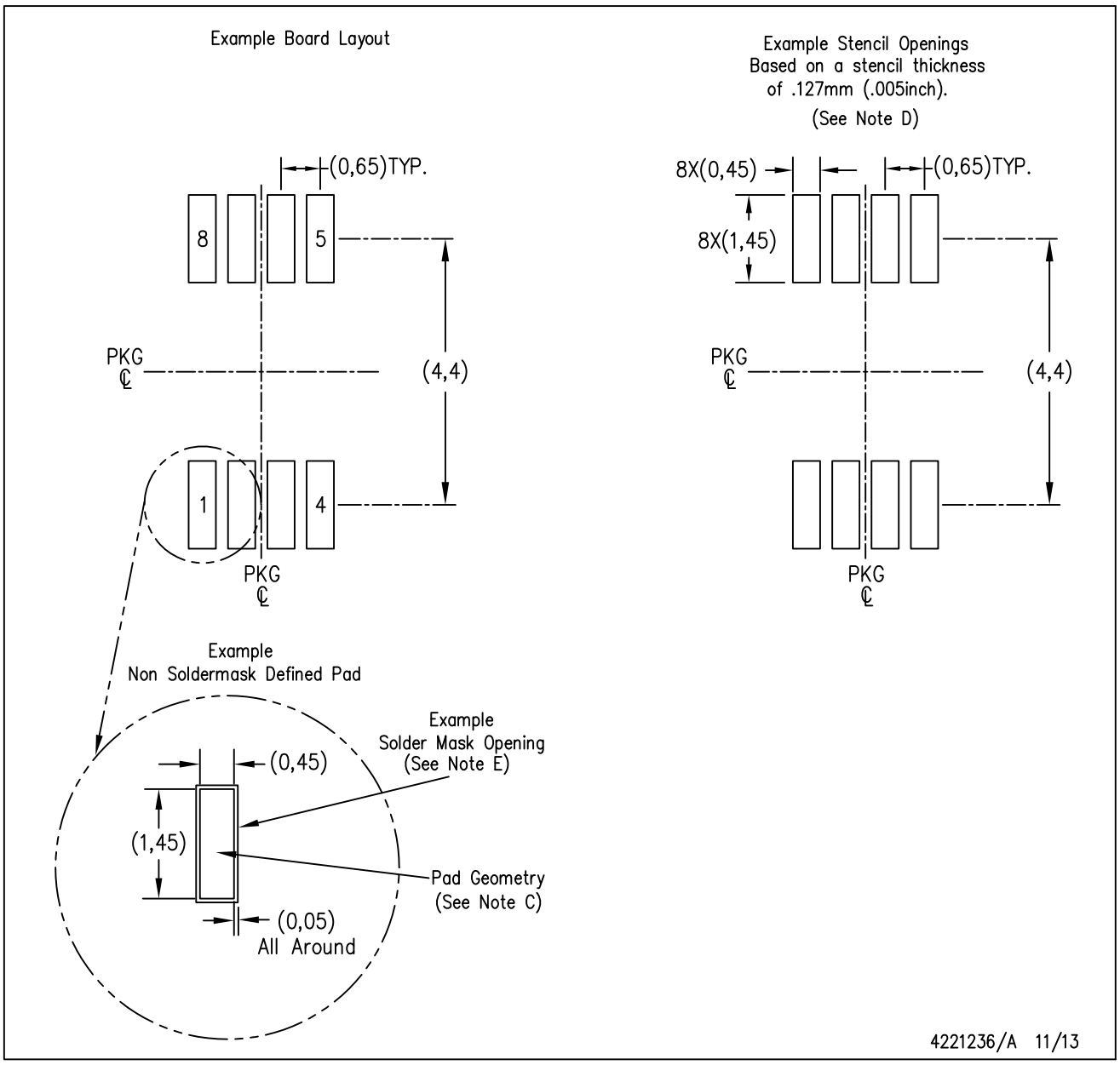
DGK (S–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



4073329/E 05/06

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
E. Falls within JEDEC MO–187 variation AA, except interlead flash.

DGK (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE



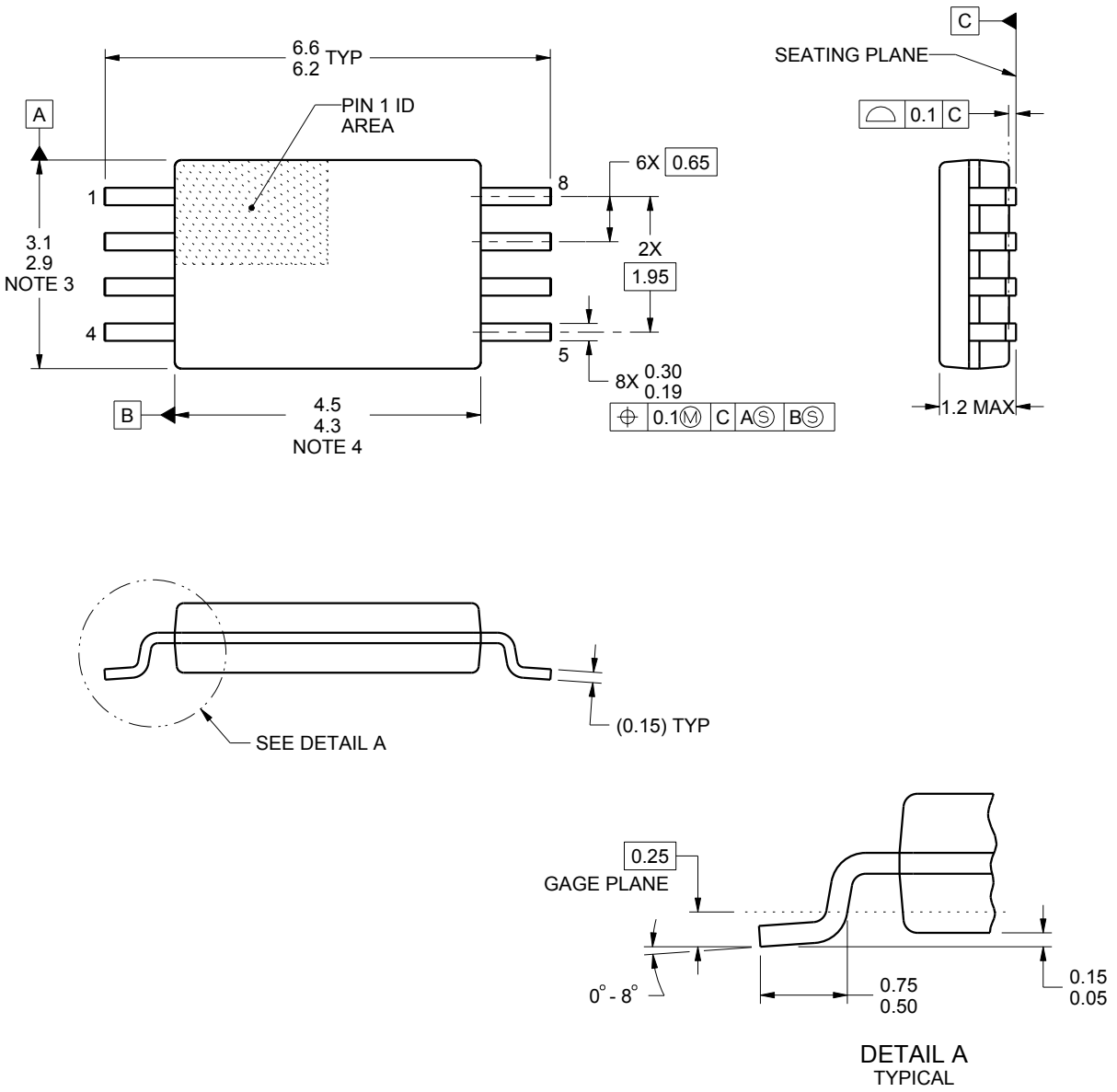
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PACKAGE OUTLINE

PW0008A

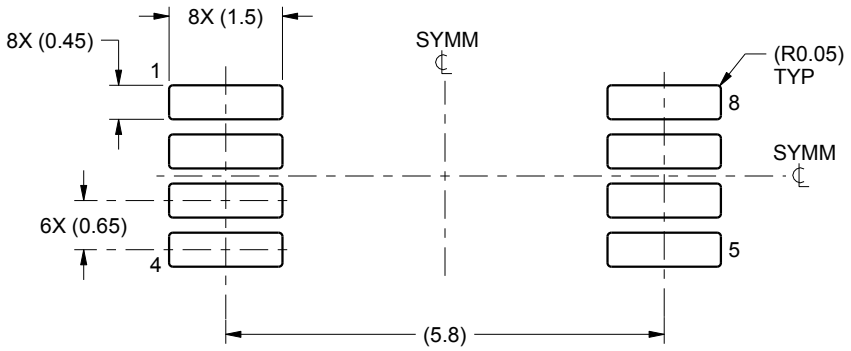
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

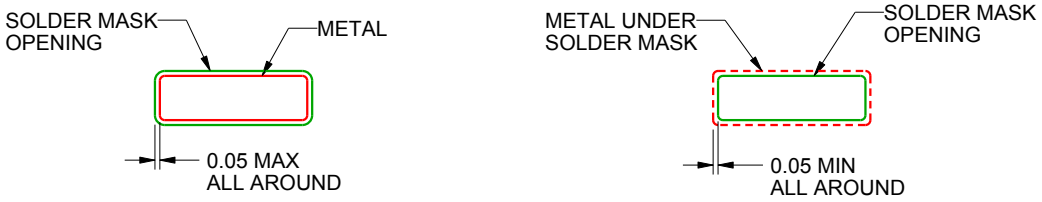


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153, variation AA.



LAND PATTERN EXAMPLE
SCALE:10X

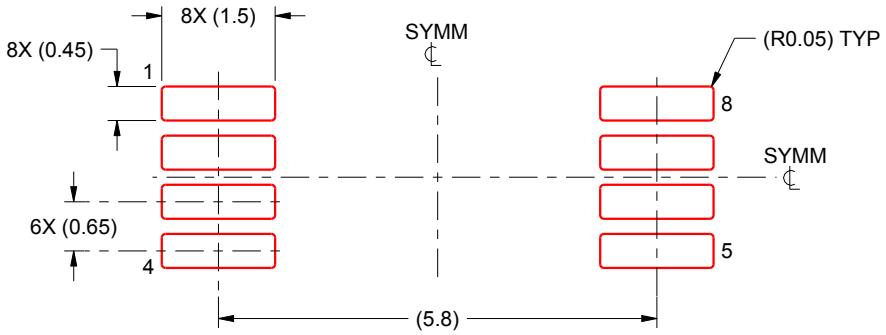


SOLDER MASK DETAILS
NOT TO SCALE

4221848/A 02/2015

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



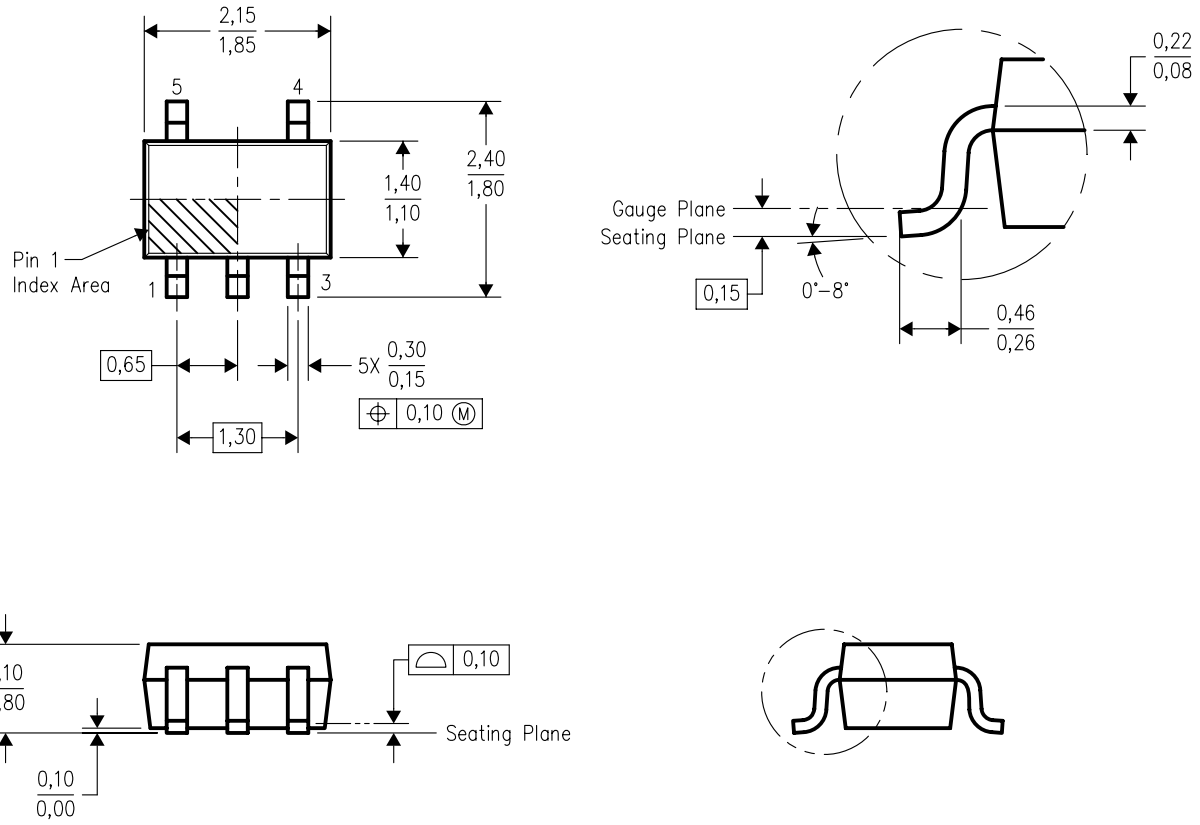
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:10X

4221848/A 02/2015

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

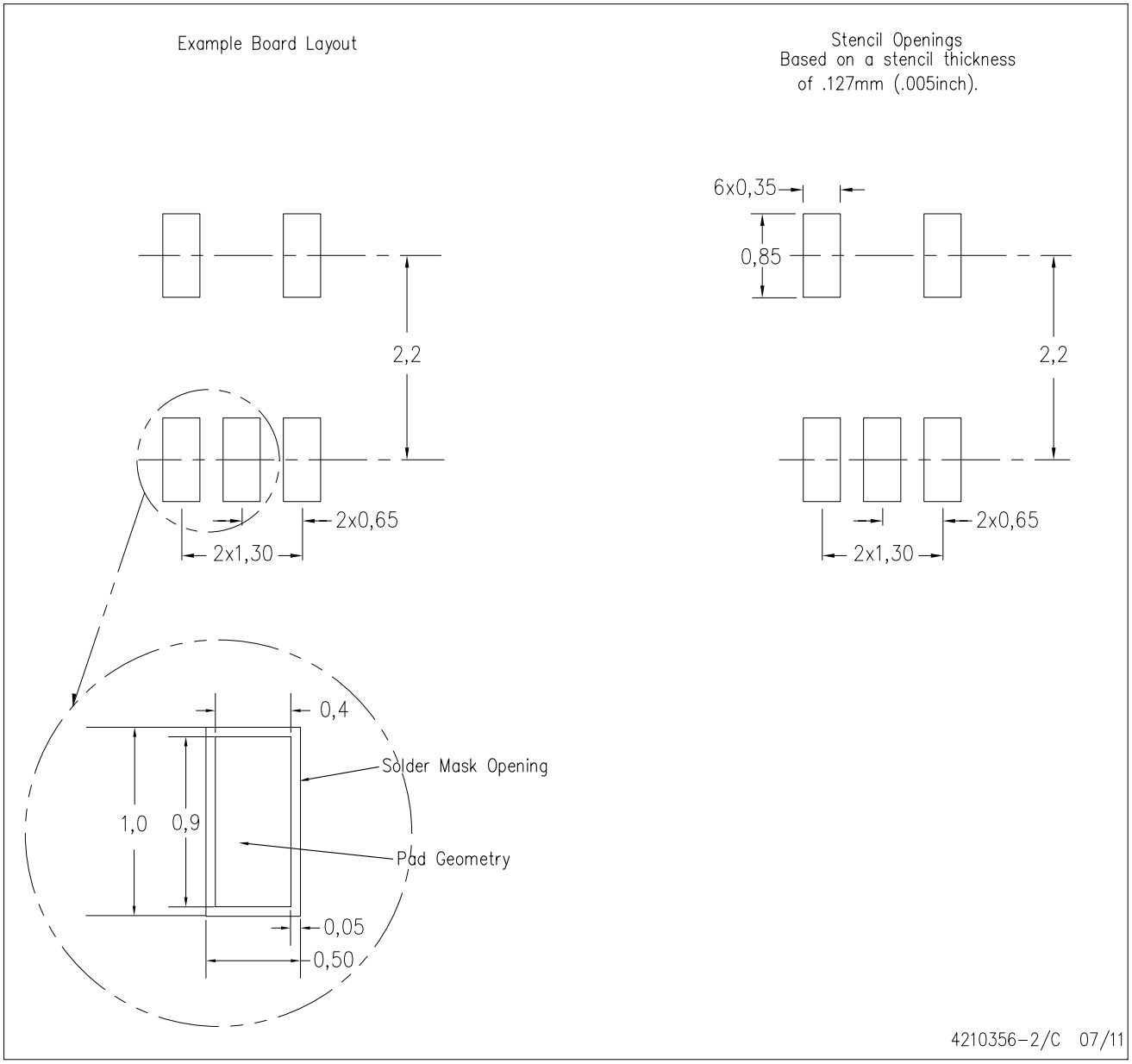
DCK (R–PDSO–G5) PLASTIC SMALL–OUTLINE PACKAGE



4093553–3/G 01/2007

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–203 variation AA.

DCK (R–PDSO–G5) PLASTIC SMALL OUTLINE



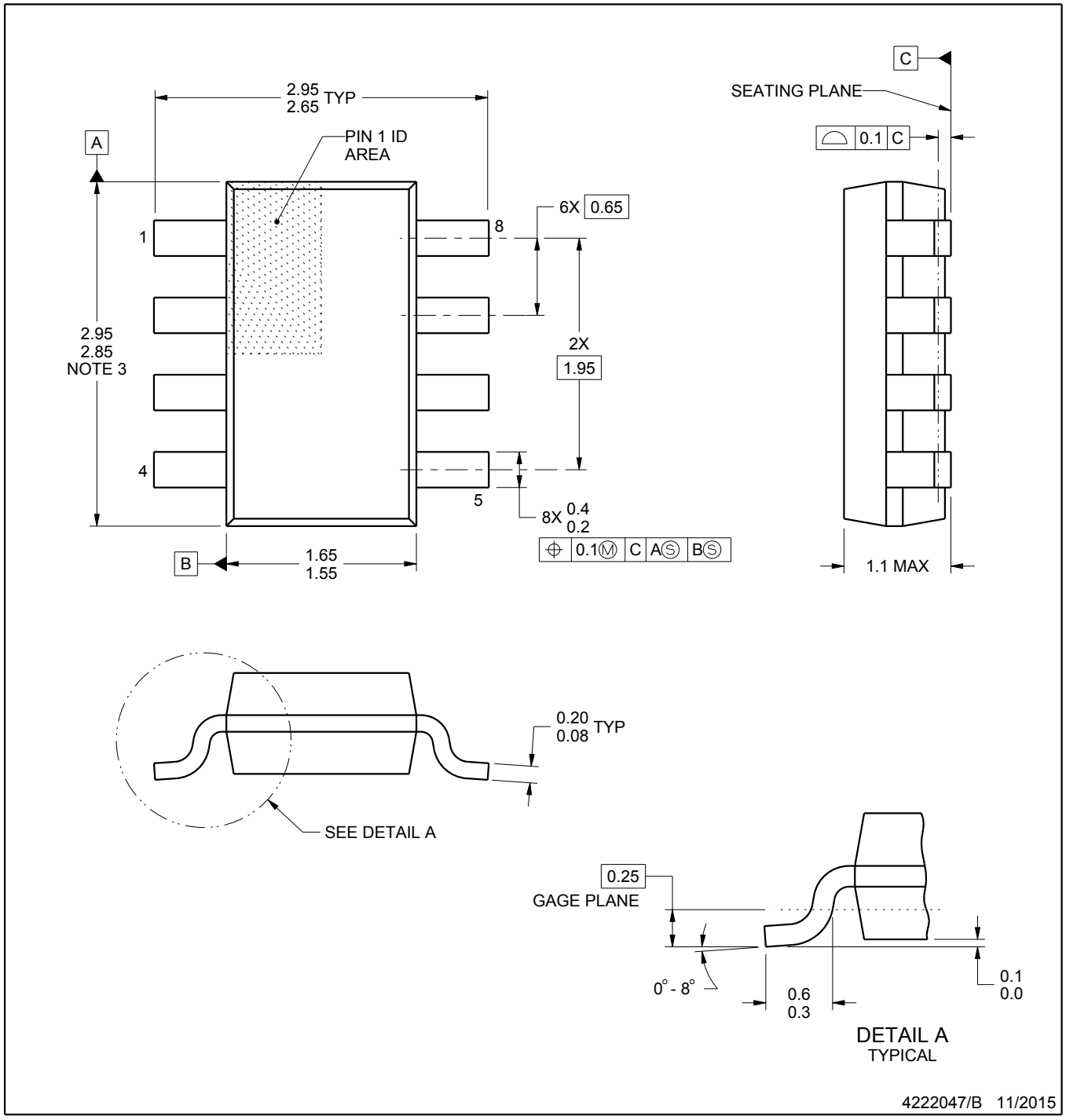
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.

PACKAGE OUTLINE

DDF0008A

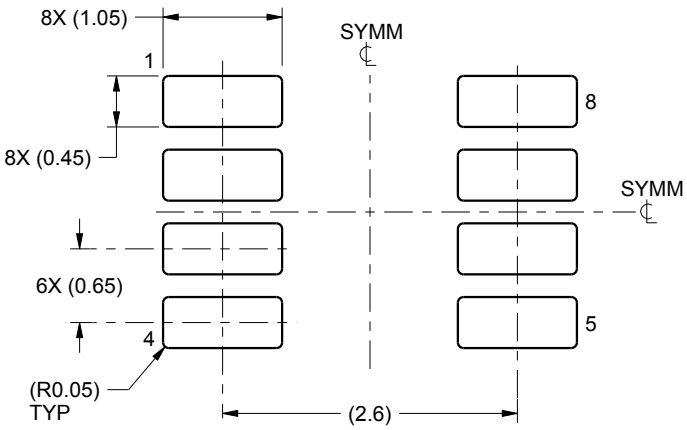
SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE

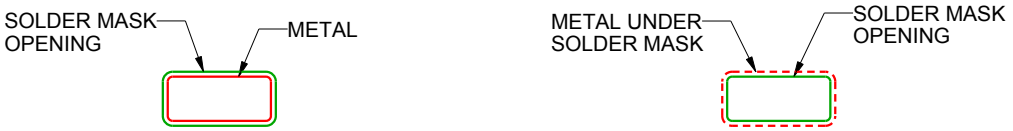


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



LAND PATTERN EXAMPLE
SCALE:15X



NON SOLDER MASK
DEFINED

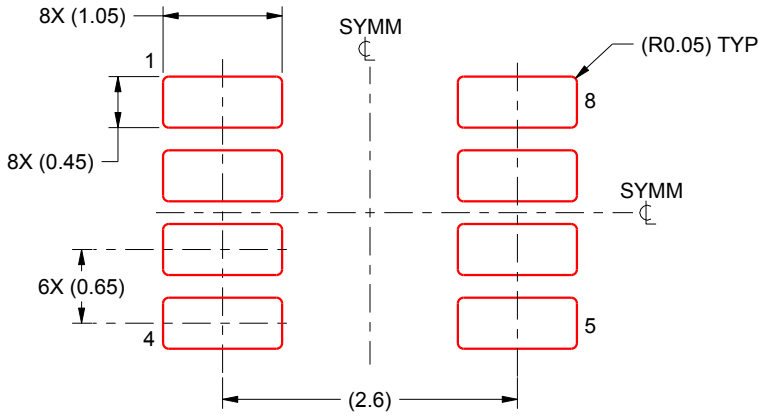
SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4222047/B 11/2015

NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4222047/B 11/2015

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

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